L Number	Hits	Search Text	DB	Time stamp
1	132	nanocrystalline and amorphous and silicon	USPAT;	2003/08/20 11:47
		adj carbide	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB]
2	0	nanocrystalline near20 amorphous near20	USPAT;	2003/08/20 11:47
		silicon adj carbide	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	[
3	4	nanocrystalline same amorphous same	USPAT;	2003/08/20 12:23
		silicon adj carbide	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

	1.53	1 /70 C101C12 0 70 C122E07 0	TTODAM	1 0000 100 100 00
4	157	(US-6121633-\$ or US-6133587-\$ or	USPAT;	2003/08/20 12:07
		US-6297521-\$ or US-6306691-\$ or	US-PGPUB;	
		US-6313482-\$ or US-6249020-\$ or	EPO; JPO;	
		US-6365919-\$ or US-6075259 - \$ or	DERWENT	
		US-5323040-\$ or US-6130147-\$ or	·	
1		US-5698869-\$ or US-5465249-\$ or		
		US-4113515-\$ or US-4849797-\$ or		
		US-4507673-\$ or US-6031263-\$ or		
		US-5858811-\$ or US-6011279-\$ or		
		US-6049110-\$ or US-5976926-\$ or		
		US-4473836-\$ or US-5734181-\$ or		
	į	US-6383576-\$ or US-5449941-\$ or		
	-	US-5393999-\$ or US-5629222-\$).did. or	1	
		(US-5801401-\$ or US-6166401-\$ or		
1		US-6018166-\$ or US-5989958-\$ or		
		US-6180958-\$ or US-6344663-\$ or		
		US-5886368-\$ or US-5039354 - \$ or		
		US-4826778-\$ or US-6163066-\$ or		
		US-6084248-\$ or US-6099574-\$ or		
		US-5260560-\$ or US-5159424-\$ or		
		US-5056897-\$ or US-5451798-\$ or		
		US-5369040-\$ or US-6166319-\$ or		1
1		US-6093937-\$ or US-6144581-\$ or		1
		US-5539217-\$ or US-5371383-\$ or		
1	1	US-5719410-\$ or US-5661312-\$ or	}	1
		US-5672889-\$ or US-5798548-\$ or		1
	1	US-5506421-\$).did. or (US-6562131-\$ or		1
1		US-6547877-\$ or US-6562130-\$ or	1	1
				1
	1	US-6537371-\$ or US-5030580-\$ or		
		US-4189826-\$ or US-5932902-\$ or		
1	İ	US-4598305-\$ or US-5449925-\$ or		
		US-5441901-\$ or US-6236590-\$ or		
		US-4462150-\$ or US-4460670-\$ or		
		US-4657699-\$ or US-5604357-\$ or		İ
		US-5580380-\$ or US-5623442-\$ or		
		US-5654208-\$ or US-5670790-\$ or		
		US-5714766-\$ or US-5740104-\$ or		
1				
		US-5754477-\$ or US-5786250-\$ or		
		US-5789276-\$ or US-5846859-\$ or		
		US-5877041-\$ or US-5907775-\$).did. or		
		(US-6034001-\$ or US-5886379-\$ or		
		US-5557122-\$ or US-5866930-\$ or		
		US-5808336-\$ or US-5508543-\$ or		
		US-5898197-\$ or US-6351411-\$ or		
		US-6178112-\$ or US-6205052-\$ or		
		US-6197439-\$ or US-5640343-\$ or		
		US-5793697-\$ or US-6166948-\$ or		1
		US-6307775-\$ or US-4451391-\$ or		
		US-4768072-\$ or US-6309907-\$ or		
		US-5061976-\$ or US-5625217-\$ or		
		US-6002143-\$ or US-5852306-\$ or		
1		US-6108177-\$ or US-5408377-\$ or		
		US-5145741-\$ or US-5235195-\$ or		
1		US-5260593-\$).did. or (US-5293560-\$ or		
		US-5298796-\$ or US-5407845-\$ or		
1		US-5415126-\$ or US-5455432-\$ or		
		US-5477485-\$ or US-5530581-\$ or		
		US-5557114-\$ or US-5562769-\$ or		
		US-4841349-\$ or US-4893273-\$ or		
	1	US-5049950-\$ or US-5111430-\$ or		
		US-4738729-\$ or US-4769686-\$).did. or		
	1	(US-20010032997-\$ or US-20010049183-\$ or		
1	1	US-20020024050-\$ or US-20020137284-\$ or		
1	1	US-20020036331-\$ or US-20020017647-\$ or		
1	1	US-20020041514-\$ or US-20030001191-\$).did.		
	1	or (EP-291951-\$ or EP-681333-\$ or		1
	1	US-5585986-\$).did. or (JP-63289960-\$ or		†
	1	JP-01115162-\$ or JP-63219172-\$ or		
	1	JP-63181473-\$ or JP-62122275-\$ or		
		JP-04056769-\$ or JP-03222367-\$ or		
		JP-02203564-\$ or JP-56056677-\$ or		}
		JP-06302828-\$ or JP-07226507-\$ or		
Coaret II'	d+ 0 x - 0	JP, 08255878, \$ Ar JP 60184681 \$ or		
Search His	acory 8/	JP-09255878 s or JP-60184681 s or JP-60242678-\$ or JP-06224431-\$ or		
C:\APPS\EA	4ST\Workspa	CAR WARESPACES HIS CALONOMAN 0-\$).did. or		1
1	1			l

2003/08/20 12:08					
EPO, JPC, DERMENT USPAT	5	0	ultra-amorphous near6 nanocrystalline		2003/08/20 12:08
DERMENT USPAT US				•	
Comparison		j			
US-RGUUS, EPO, JPO, DERMENT US-RGUUS, EPO, JPO, DERMENT US-RGUIS, EPO, JPO, DERMENT US-RGUIS, LEO, JPO, LEO, LEO				i .	
The composition of the composi	6	0	ultra-amorphous		2003/08/20 12:08
0					
1				1	
S					
B	7	0	ultra adj amorphous	-	2003/08/20 12:08
Carbon adj gate				1	
S					
10					
Second Second	8	26	carbon adj gate	1	2003/08/20 12:46
Server Derivative Derivat					
10					
9					
10 2 ("4598305").PN. EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT:	9	4	(carbon adj gate "carbon gate") and		2003/08/20 13:04
DERMENT; TEM TDB USFAT; US-PGPUB; EPO, JPO; DERWENT; US-PGPUB; EPO, JPO; DERWENT; US-PGPUB; EPO, JPO; DERWENT; US-PGPUB; EPO, JPO; DERWENT; USFAT; US			float\$3 near4 gate and control adj gate		
The TDB					
10 2 ("4598305").PN. US_FR; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USFAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USFAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USFAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USFAT US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USFAT US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USFAT US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USFAT US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USFAT US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USFAT US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USFAT US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USFAT US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USFAT US_PGPUB; EPO; JPO; DERWENT; US_PGPUB; EPO; JPO;					
11 2 ("4994401").PN. US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT USPAT					
11 2 ("4994401").PN.	10	2	("4598305").PN.		2003/08/20 13:04
11					
TBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT 2003/08/20 13:04 2003/08/					
11					
- 13 (("4113515") or ("4473836") or ("5698869") or ("5858811") or ("5084248") or ("6093937") or ("6099574") or ("6130147") or ("6163163") or ("6084248") or ("6093937") or ("616301") or ("6163016") or ("6164501")).PN 13 (US-6144581-\$ or US-6163066-\$ or US-64473836-\$ or US-5976926-\$ or US-6431263-\$ or US-5976926-\$ or US-603317-\$).did 1 hartstein.in. and low adj voltage adj memory.ti. o jp-63289960\$-\$.did. o jp-363289960\$-\$.did. o jp-363289960\$-\$.did. o jp-363289960-\$.did. o jp-063219172\$-\$.did. - 2 3 takashi.in. and carrier near6 silicon adj substrate - 3 diamond adj layer near6 process cliamond adj layer near6 process cliamond adj layer near6 process) and silicon adj carbide - 1 takashi.in. and ito.in. and igfet o jp-063219172\$-\$.did. - 2 jp-63219172\$-\$.did. - 3 jp-63219172\$-\$.did 4 jp-63219172\$-\$.did 5 jp-63219172\$-\$.did 5 jp-63219172\$-\$.did 6 jp-63219172\$-\$.did 7 jp-63219172\$-\$.did 7 jp-63219172\$-\$.did 8 jp-63219172\$-\$.did 9 jp-63219172\$-\$.did 10 jp-63219172\$-\$.did 11 jp-63219172\$-\$.did 12 jp-63219172\$-\$.did 13 jp-63219172\$-\$.did 14 jp-63219172\$-\$.did 15 jp-63219172\$-\$.did 16 jp-63219172\$-\$.did 17 jp-63219172\$-\$.did.					
- 13 (("4113515") or ("4473836") or ("5698869") or ("5698869") or ("5698861") or ("6031263") or ("6082428") or ("6093937") or ("6099574") or ("61644581") or ("61643066") or ("6166401")).PN 13 (US-616401-\$ or US-6163066-\$ or US-616304248-\$ or US-616401-\$ or US-5976926-\$ or US-6031263-\$ or US-5976926-\$ or US-6031263-\$ or US-5976926-\$ or US-6031263-\$ or US-6099574-\$ or US-6130147-\$).did 1 hartstein.in. and low adj voltage adj memory.ti 0 jp-632899605-\$.did. 0 jp-3632899605-\$.did. 1 batkashi.in. and carrier near6 silicon adj substrate - 3 takashi.in. and carrier near6 silicon adj substrate - 38 diamond adj layer near6 process (diamond adj layer near6 process) and silicon adj carbide silicon adj carbide takashi.in. and ito.in. and igfet pp-0.46219172\$-\$.did 1 takashi.in. and ito.in. and igfet pp-0.662219172\$-\$.did 2 jp-63219172\$-\$.did 2 jp-63219172\$-\$.did 2 jp-63219172\$-\$.did 3 takashi.in. and ito.in. and igfet pp-0.662219172\$-\$.did 1 takashi.in. and ito.in. and igfet pp-0.662219172\$-\$.did 1 takashi.in. and ito.in. and igfet pp-0.662219172\$-\$.did 2 jp-63219172\$-\$.did 2 jp-63219172\$-\$.did 3 takashi.in. and ito.in. and igfet pp-0.662219172\$-\$.did 1 takashi.in. and ito.in. and igfet pp-0.662219172\$-\$.did 2 jp-63219172\$-\$.did.	11	2	("4994401").PN.	-	2003/08/20 13:04
- 13 (("4113515") or ("4473836") or ("5698869") or ("5698869") or ("6031263") or ("6084248") or ("6099377") or ("6099574") or ("6130147") or ("614581") or ("6163066") or ("616401")).PN 13 (US-6144581-5 or US-6163066-\$ or US-6031263-\$ or US-6039377-\$ or US-6031263-\$ o					
13					
- 13 (("4113515") or ("4473836") or ("5698869") or ("5988811") or ("5976926") or ("6093263") or ("6093263") or ("6093937") or ("6099574") or ("6130147") or ("6164581") or ("6163066") or ("6166401")).PN. - 13 (US-6144581-\$ or US-6163066-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5698869-\$ or US-6031263-\$ or US-5698869-\$ or US-6031263-\$ or US-6099574-\$ or US-6031263-\$ or US-6099574-\$ or US-6031263-\$ or US-6099574-\$ or US-603937-\$ or US-6099574-\$ or US-6031263-\$ or US-6099574-\$ or US-6031263-\$ or US-6099574-\$ or US-6099574-\$ or US-6031263-\$ or US-6099574-\$ or US-60999574-\$ or US-60999595-\$ or US-60999574-\$ or US-60999574-\$ or US-60999595-\$ or US-60999574-\$ or US-60999574-\$ or US-60999595-\$ or US-60999595-\$ or US-60999574-\$ or US-60999595-\$ or US-60					
or ("5858811") or ("5976926") or ("6093937") or ("6031263") or ("6084248") or ("6093937") or ("6144581") or ("6130147") or ("6144581") or ("6163066") or ("6164601").PN. 13 (US-6144581-\$ or US-6163066-\$ or US-616401-\$ or US-4113515-\$ or US-4113515-\$ or US-4133836-\$ or US-5858811-\$ or US-5976926-\$ or US-693937-\$ or US-6093937-\$ or US-603209574-\$ or US-6130147-\$).did. -					
("6031263") or ("6084248") or ("6093937") or ("61699574") or ("6163066") or ("61644581") or ("6163066") or ("61644581") or ("61644581") or ("6163066") or ("61644581") or US-6163066-\$ or US-6163066-\$ or US-4473836-\$ or US-5698869-\$ or US-4473836-\$ or US-5698869-\$ or US-6031263-\$ or US-6084248-\$ or US-6031263-\$ or US-6099574-\$ or US-6130147-\$).did.	-	13		USPAT	2003/08/18 17:22
or ("6099574") or ("6130147") or ("6144581") or ("6164001")).PN. 13 (US-6144581-\$ or US-6163066-\$ or US-616401-\$ or US-6163066-\$ or US-616401-\$ or US-6163066-\$ or US-616401-\$ or US-5976926-\$ or US-6031263-\$ or US-598869-\$ or US-6033263-\$ or US-6093574-\$ or US-6130147-\$).did. 1 hartstein.in. and low adj voltage adj memory.ti. 0 jp-63289960\$-\$.did. 0 jp-363289960\$-\$.did. 0 jp-0363289960\$-\$.did. 1 takashi.in. and carrier near6 silicon adj substrate 1 takashi.in. and carrier near6 silicon adj substrate 2 diamond adj layer near6 process didinond adj layer near6 process and silicon adj carbide 1 takashi.in. and ito.in. and igfet silicon adj carbide 2 jp-063219172\$-\$.did. 2 jp-63219172\$-\$.did. 3 takashi.in. and ito.in. and igfet spot jPO; DERWENT; lBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; lBM TDB USPAT; US-PGPUB; EPO;					
- 13 ("6144581") or ("6163066") or ("6166401").PN. 13 (US-6144581-\$ or US-6163066-\$ or US-6166401-\$ or US-4133515-\$ or US-6166401-\$ or US-5698869-\$ or US-5858811-\$ or US-5698869-\$ or US-6031263-\$ or US-6031263-\$ or US-6031263-\$ or US-6039574-\$ or US-630147-\$).did. - 1 hartstein.in. and low adj voltage adj memory.ti. - 0 jp-63289960\$-\$.did. 0 jp-363289960\$-\$.did.	}			:	
Comparison of the content of the c					
13					,
US-6166401-\$ or US-4113515-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6099574-\$ or US-6130147-\$).did. - 1 hartstein.in. and low adj voltage adj memory.ti 0 jp-63289960\$-\$.did 0 jp-363289960\$-\$.did 1 takashi.in. and carrier near6 silicon adj substrate - 3 takashi.in. and carrier near6 silicon adj substrate - 38 diamond adj layer near6 process didicon adj layer near6 process (diamond adj layer near6 process) and silicon adj layer near6 process of diamond adj layer near6 process of di		1.0			0000/05/10 11 00
US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$ or US-6033937-\$ or US-6099574-\$ or US-6130147-\$).did. - 1 hartstein.in and low adj voltage adj memory.ti 0 jp-63289960\$-\$.did 0 jp-363289960\$-\$.did 0 jp-0363289960\$-\$.did 0 jp-0363289960\$-\$.did 1 takashi.in. and carrier near6 silicon adj substrate - 3 takashi.in. and carrier near6 silicon adj substrate - 38 diamond adj layer near6 process diamond adj layer near6 process of diamond adj layer nea	_	13		USPAT	2002/05/10 11:29
US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6031263-\$ or US-609574-\$ or US-6130147-\$).did. - 1 hartstein.in. and low adj voltage adj memory.ti. - 0 jp-63289960\$-\$.did 0 jp-63289960\$-\$.did 0 jp-0363289960\$-\$.did 1 takashi.in. and carrier near6 silicon adj substrate - 3 takashi.in. and carrier near6 silicon adj substrate - 3 takashi.in. and carrier near6 silicon adj substrate - 3 takashi.in. and carrier near6 silicon adj substrate - 4 takashi.in. and carrier near6 silicon adj substrate - 5 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 6 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 7 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 8 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 9 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 1 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 1 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 1 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 1 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 1 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 2 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 2 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 2 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 2 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 2 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did.					
US-6031263-\$ or US-6084248-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$).did. hartstein.in. and low adj voltage adj memory.ti. jp-63289960\$-\$.did. USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:34 USPAT 2002/05/10 11:36 Substrate 3 takashi.in. and carrier near6 silicon adj substrate diamond adj layer near6 process (diamond adj layer near6 process) and silicon adj carbide takashi.in. and ito.in. and igfet jp-063219172\$-\$.did. 2 jp-63219172\$-\$.did. DERWENT 2002/05/10 11:39 2002/05/10 11:45 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT;					
US-6093937-\$ or US-6099574-\$ or US-6130147-\$).did. hartstein.in. and low adj voltage adj memory.ti. 0 jp-63289960\$-\$.did. jp-0363289960\$-\$.did. jp-0363289960\$-\$.did. USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:36 substrate 1 takashi.in. and carrier near6 silicon adj substrate diamond adj layer near6 process DERWENT 2002/05/10 11:38 substrate diamond adj layer near6 process DERWENT 2002/05/10 11:38 silicon adj carbide takashi.in. and ito.in. and igfet USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT;					
US-6130147-\$).did. hartstein.in. and low adj voltage adj memory.ti. 0 jp-63289960\$-\$.did. 0 jp-363289960\$-\$.did. USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:34 USPAT 2002/05/10 11:34 USPAT 2002/05/10 11:34 USPAT 2002/05/10 11:34 USPAT 2002/05/10 11:34 USPAT 2002/05/10 11:34 USPAT 2002/05/10 11:35 Substrate USPAT 2002/05/10 11:36 USPAT 2002/05/10 11:36 USPAT 2002/05/10 11:36 USPAT 2002/05/10 11:36 USPAT 2002/05/10 11:36 Substrate USPAT 2002/05/10 11:38 Substrate USPAT 2002/05/10 11:38 Substrate USPAT 2002/05/10 11:38 Substrate USPAT 2002/05/10 11:39 USPAT: USPAT; USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; USPGPUB; EPO; JPO; DERWENT; USPGPUB; EPO; JPO; DERWENT; USPGPUB; EPO; JPO; DERWENT;					
- hartstein.in. and low adj voltage adj memory.ti. jp-63289960\$-\$.did. USPAT 2002/05/10 11:30 10 10 10 10 11 11 11					
- 0 jp-363289960\$-\$.did 0 jp-363289960\$-\$.did 0 jp-363289960\$-\$.did 0 jp-363289960\$-\$.did 1 takashi.in. and carrier near6 silicon adj substrate - 3 takashi.in. and carrier near6 silicon adj substrate - 38 diamond adj layer near6 process - 2 (diamond adj layer near6 process) and silicon adj carbide - 1 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 2 jp-63219172\$-\$.did 2 jp-63219172\$-\$.did 3 jp-63219172\$-\$.did 4 jp-63219172\$-\$.did 5 jp-63219172\$-\$.did 6 jp-63219172\$-\$.did 7 jp-63219172\$-\$.did 8 jp-63219172\$-\$.did 9 jp-63219172\$-\$.did 1 jp-63219172\$-\$.did 1 jp-63219172\$-\$.did 1 jp-63219172\$-\$.did.	_	1		FPO	2002/05/10 11:20
- 0 jp-63289960\$-\$.did.	-			L PO	2002/05/10 11:28
- 0 jp-363289960\$-\$.did. 0 jp-0363289960\$-\$.did. 1 takashi.in. and carrier near6 silicon adj substrate - 3 takashi.in. and carrier near6 silicon adj substrate - 38 diamond adj layer near6 process (diamond adj layer near6 process) and silicon adj carbide - 1 takashi.in. and ito.in. and igfet - 0 jp-063219172\$-\$.did. - 2 jp-63219172\$-\$.did. USPAT 2002/05/10 11:30 USPAT 2002/05/10 11:38 DERWENT 2002/05/10 11:38 DERWENT 2002/05/10 11:39 DERWENT 2002/05/10 11:45 USPAT; USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; USPGPUB; EPO; JPO; DERWENT;	_	ا م		IISPAT	2002/05/10 11.20
- 0 jp-0363289960\$-\$.did. 1 takashi.in. and carrier near6 silicon adj substrate - 3 takashi.in. and carrier near6 silicon adj substrate - 38 diamond adj layer near6 process didamond adj layer near6 process) and silicon adj carbide - 1 takashi.in. and ito.in. and igfet jp-063219172\$-\$.did 2 jp-63219172\$-\$.did 2 jp-63219172\$-\$.did 2 jp-63219172\$-\$.did 36 USPAT USPAT 2002/05/10 11:34 2002/05/10 11:38 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:45 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:45 2002/05/10 11:47 2002/05/10 11:45 2002/05/10 11:47 2002/05/10 11:45 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:45 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:45 2002/05/10 11:47 2002/05/10 11:45 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:45 2002/05/10 11:47 2	_	1			
1 takashi.in. and carrier near6 silicon adj substrate 2 3 takashi.in. and carrier near6 silicon adj substrate 3 takashi.in. and carrier near6 silicon adj substrate 4 diamond adj layer near6 process 5 diamond adj layer near6 process and silicon adj carbide 5 takashi.in. and ito.in. and igfet 6 takashi.in. and ito.in. and igfet 7 p-063219172\$-\$.did. 2 p-63219172\$-\$.did. 2 p-63219172\$-\$.did. 2 p-63219172\$-\$.did. 2 p-63219172\$-\$.did. 3 takashi.in. and carrier near6 silicon adj JPO 2002/05/10 11:38 2 pERWENT 2002/05/10 11:39 2 pERWENT 2002/05/10 11:45 2 per JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; DERWE		· .			
substrate takashi.in. and carrier near6 silicon adj substrate diamond adj layer near6 process (diamond adj layer near6 process) and silicon adj carbide takashi.in. and ito.in. and igfet jp-063219172\$-\$.did. 2 jp-63219172\$-\$.did. Substrate diamond adj layer near6 process DERWENT DERWENT 2002/05/10 11:39 DERWENT 2002/05/10 11:45 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	_	1			
- 3 takashi.in. and carrier near6 silicon adj substrate - 38 diamond adj layer near6 process - 2 (diamond adj layer near6 process) and silicon adj carbide - 1 takashi.in. and ito.in. and igfet - 0 jp-063219172\$-\$.did. - 2 jp-63219172\$-\$.did. 3 takashi.in. and carrier near6 silicon adj JPO		1		001111	2002,00,10 11.50
substrate diamond adj layer near6 process (diamond adj layer near6 process) and silicon adj carbide takashi.in. and ito.in. and igfet jp-063219172\$-\$.did. 2 jp-63219172\$-\$.did. DERWENT 2002/05/10 11:39 2002/05/10 11:45 EPO USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	_	٦		JPO	2002/05/10 11.38
- 38 diamond adj layer near6 process (diamond adj layer near6 process) and silicon adj carbide - 1 takashi.in. and ito.in. and igfet - 0 jp-063219172\$-\$.did. - 2 jp-63219172\$-\$.did. 2002/05/10 11:39 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:47 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45 2002/05/10 11:45]		31.0	=====================================
- 2 (diamond adj layer near6 process) and silicon adj carbide - 1 takashi.in. and ito.in. and igfet - 0 jp-063219172\$-\$.did. - 2 jp-63219172\$-\$.did. 2 jp-63219172\$-\$.did. 2 jp-63219172\$-\$.did. 2 jp-63219172\$-\$.did. 2 jp-63219172\$-\$.did. 2 jp-63219172\$-\$.did. 2 jp-63219172\$-\$.did. 2 jp-63219172\$-\$.did. 2 jp-63219172\$-\$.did.	_	38		DERWENT	2002/05/10 11:39
silicon adj carbide takashi.in. and ito.in. and igfet jp-063219172\$-\$.did. 2 jp-63219172\$-\$.did. silicon adj carbide takashi.in. and ito.in. and igfet USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	-			1.	
- 1 takashi.in. and ito.in. and igfet 0 jp-063219172\$-\$.did.					====, ==, ==
- 0 jp-063219172\$-\$.did. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	_	1		EPO	2002/05/10 11:45
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	_				· ·
EPO; JPO; DERWENT; IBM_TDB 2 jp-63219172\$-\$.did. USPAT; US-PGPUB; EPO; JPO; DERWENT;					
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;				· ·	
1BM_TDB					
- 2 jp-63219172\$-\$.did.					
US-PGPUB; EPO; JPO; DERWENT;	_	2	ip-63219172\$-\$.did.	_	2002/05/10 12:15
EPO; JPO; DERWENT;		_	 		
DERWENT;					
				· ·	
1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		[IBM TDB	

_	2	jp-63289960\$-\$.did.	USPAT;	2002/05/10 11:49
			US-PGPUB;	
			EPO; JPO;	
	}		DERWENT;	
	_		IBM_TDB	0000/05/40 44
-	2	jp-01115162\$-\$.did.	USPAT;	2002/05/10 11:49
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	jp-63181473\$ - \$.did.	USPAT;	2002/05/10 11:50
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	jp-62122275\$-\$.did.	USPAT;	2002/05/10 11:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	jp-404056769\$-\$.did.	USPAT;	2002/05/10 11:52
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	jp-04056769\$-\$.did.	USPĀT;	2002/05/10 12:02
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	796	(257/77).CCLS.	USPAT;	2002/05/10 14:04
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	9	((257/77).CCLS.) and (x near12 silicon adj	USPAT;	2002/05/10 12:18
		carbide)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	489	silicon adj carbide and gate and x and	USPAT;	2002/05/10 12:19
		source and drain	US-PGPUB;	
			EPO; JPO;	
		<u>.</u>	DERWENT;	
			IBM_TDB	
-	53	silicon adj carbide.ti,ab. and gate and x	USPĀT;	2002/05/10 12:26
	1	and source and drain	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	162	stoichiometric adj coefficient	USPAT;	2002/05/10 12:26
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	11	stoichiometric adj coefficient near x	USPĀT;	2002/05/10 12:26
	1		US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
	1		IBM_TDB	
-	30	stoichiometric adj coefficient near12 x	USPĀT;	2002/05/10 12:28
	[US-PGPUB;	*
	1		EPO; JPO;	
1			DERWENT;	
	[IBM_TDB	_ , , _ ,
-	0		USPAT;	2002/05/10 12:30
1		adj transistor	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
	L		IBM_TDB	L

_	0	"si.sub.1-x.c.sub.x"	USPAT;	2002/05/10 12:29
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	57	"si.sub.1-x" adj "c.sub.x"	USPAT;	2002/05/10 12:31
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	,
			IBM_TDB	0000/05/10 13:55
-	18		USPAT;	2002/05/10 13:55
		fet or nmosfet or pmosfet or field adj effect adj transistor or dtmosfet or gate)	US-PGPUB; EPO; JPO;	
		effect adj transistor of dimosfet of gate,	DERWENT;	
			IBM TDB	
-	15	"si.sub.1-x" adj "c.sub.x" and (mosfet or	USPAT;	2002/05/10 13:57
		fet or nmosfet or pmosfet or field adj	US-PGPUB;	
		effect adj transistor or dtmosfet or (gate	EPO; JPO;	
		and (source or drain)))	DERWENT;	
		44055 455 455 455 455 455 455 455 455 45	IBM_TDB	2002/05/12 11 25
-	179	((257/77).CCLS.) and (silicon carbide or	USPAT;	2002/05/10 14:07
		"si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x	US-PGPUB; EPO; JPO;	
		c.i A or Si.y. c.i-y / and x	DERWENT;	
			IBM TDB	
-	50	((257/77).CCLS.) and (silicon carbide or	USPAT;	2002/05/10 14:15
		"si.1-x. c.x." or "si.1-y. c.y." or "si.x.	US-PGPUB;	,
		c.1-x" or "si.y. c.1-y") and x and (source	EPO; JPO;	
		same drain) and gate and (mosfet or	DERWENT;	
		nmosfet or pmosfet or dtmosfet or cmosfet	IBM_TDB	
	1	or fet or field adj effect adj transistor) ((257/77).CCLS.) and (silicon carbide or	USPAT;	2002/05/10 14:10
-	1	"si.1-x. c.x." or "si.1-y. c.y." or "si.x.	US-PGPUB;	2002/03/10 14:10
		c.1-x" or "si.y. c.1-y") and x and (source	EPO; JPO;	
		same drain) and gate and (mosfet or	DERWENT;	
		nmosfet or pmosfet or dtmosfet or cmosfet	IBM_TDB	
		or fet or field adj effect adj transistor)		
	1	and barrier adj energy	HCDAM.	2002/05/10 14.24
_	30	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x.	USPAT; US-PGPUB;	2002/05/10 14:24
Ī		c.1-x or "si.y. $c.1-y$ ") and x and (source	EPO; JPO;	
		same drain) and gate and (mosfet or	DERWENT;	
		nmosfet or pmosfet or dtmosfet or cmosfet	IBM TDB	
		or fet or field adj effect adj transistor)	_	
		and barrier		0000/0=/==
_	0	((257/77).CCLS.) and ("si.1-x. c.x." or	USPAT;	2002/05/10 14:26
		"si.1-y. c.y." or "si.x. c.1-x" or "si.y.	US-PGPUB;	
		c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or	EPO; JPO; DERWENT;	
		dtmosfet or cmosfet or fet or field adj	IBM TDB	
		effect adj transistor) and barrier		
-	0	((257/77).CCLS.) and ("si.1-x. c.x." or	USPAT;	2002/05/10 14:20
		"si.1-y. c.y." or "si.x. c.1-x" or "si.y.	US-PGPUB;	
		c.1-y") and x and (source same drain) and	EPO; JPO;	
		gate and (mosfet or nmosfet or pmosfet or	DERWENT;	
		dtmosfet or cmosfet or fet or field adj	IBM_TDB	
_	0	effect adj transistor) ("si.1-x. c.x." or "si.1-y. c.y." or	USPAT;	2002/05/10 14:20
		"si.x. c.1-x" or "si.y. c.1-y") and x and	US-PGPUB;	
		(source same drain) and gate and (mosfet	EPO; JPO;	
		or nmosfet or pmosfet or dtmosfet or	DERWENT;	
		cmosfet or fet or field adj effect adj	IBM_TDB	
		transistor)	tionam.	2002/05/10 14:00
-	0	("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and	USPAT; US-PGPUB;	2002/05/10 14:20
		(mosfet or nmosfet or pmosfet or dtmosfet	EPO; JPO;	
	1	or cmosfet or fet or field adj effect adj	DERWENT;	
	1	transistor)	IBM TDB	

_	0	((257/77).CCLS.) and ("si.1-x. c.x." or	USPAT;	2002/05/10 14:27
		"si.1-y. c.y." or "si.x. c.1-x" or "si.y.	US-PGPUB;	
		c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)")	EPO; JPO;	
		and x and (source same drain) and gate and	DERWENT;	
		(mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj	IBM_TDB	Į
		transistor) and barrier		
_	30	((257/77).CCLS.) and (silicon carbide or	USPAT;	2002/05/10 14:49
-]	"si.1-x. c.x." or "si.1-y. c.y." or "si.x.	US-PGPUB;	2002/03/10 14:45
		c.1-x" or "si.y. c.1-y" or "si(x) $c(1-x)$ "	EPO; JPO;	
		or " $si(1-x)c(x)$ ") and x and (source same	DERWENT;	
		drain) and gate and (mosfet or nmosfet or	IBM TDB]
		pmosfet or dtmosfet or cmosfet or fet or	_	
		field adj effect adj transistor) and		
		barrier		
-	30	((257/77).CCLS.) and (silicon carbide or	USPAT;	2002/05/10 14:51
		"si.1-x. c.x." or "si.1-y. c.y." or	US-PGPUB;	
		("si.x. c.1-x" or "si.y. c.1-y" or	EPO; JPO;	
		"si(x)c(1-x)" or $"si(1-x)c(x)")$ near12	DERWENT;	
,		gate) and x and (source same drain) and	IBM_TDB	
		(mosfet or nmosfet or pmosfet or dtmosfet		
		or cmosfet or fet or field adj effect adj		
	E 2	transistor) and barrier	HCDATT.	2002/05/10 14.50
-	53	((257/77).CCLS.) and (silicon carbide or	USPAT;	2002/05/10 14:52
		"si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or	US-PGPUB; EPO; JPO;	
		"si(x) c(1-x)" or "si(1-x) c(x)") near12	DERWENT;	
		gate) near12 x and (257/\$6.ccls. or	IBM TDB	
		438/\$6.ccls. or 361/\$6.ccls.)	10:1-100	
_	2616	(silicon carbide or "si.1-x. c.x." or	USPAT;	2002/05/10 14:53
		"si.1-y. c.y." or ("si.x. c.1-x" or "si.y.	US-PGPUB;	
		c.1-y or "si(x)c(1-x)" or "si(1-x)c(x)")	EPO; JPO;	
		near12 gate) near12 x and (257/\$6.ccls. or	DERWENT;	
		438/\$6.ccls. or 361/\$6.ccls.)	IBM_TDB	
-	133	(silicon adj carbide or "si.1-x. c.x." or	USPAT;	2002/05/10 14:54
ļ		"si.1-y. c.y." or ("si.x. c.1-x" or "si.y.	US-PGPUB;	
		c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)")	EPO; JPO;	
ŀ		near12 gate) near12 x and (257/\$6.ccls. or	DERWENT;	
	122	438/\$6.ccls. or 361/\$6.ccls.)	IBM_TDB	2002/05/10 14-55
-	133	(silicon adj carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y.	USPAT; US-PGPUB;	2002/05/10 14:55
		c.1-y or "si(x)c(1-x)" or "si(1-x)c(x)")	EPO; JPO;	
		near6 gate) near12 x and $(257/\$6.ccls. or$	DERWENT;	
	1	438/\$6.ccls. or 361/\$6.ccls.)	IBM TDB	
-	2	((silicon adj carbide or "si.1-x. c.x." or	USPAT;	2002/05/10 15:05
		"si.1-y. c.y." or "si.x. c.1-x" or "si.y.	US-PGPUB;	
		c.1-y" or " $si(x)c(1-x)$ " or " $si(1-x)c(x)$ ")	EPO; JPO;	
		near6 gate) near12 x and (257/\$6.ccls. or	DERWENT;	
		438/\$6.ccls. or 361/\$6.ccls.)	IBM_TDB	
-	0	(("si.1-x. c.x." or "si.1-y. c.y." or	USPAT;	2002/05/10 15:09
		"si.x. c.1-x" or "si.y. c.1-y" or	US-PGPUB;	
	ĺ	"si(x)c(1-x)" or $"si(1-x)c(x)"$ or	EPO; JPO;	
		"si(a)c(1-a)" or $"si(b)c(1-b)"$ or $"si(1-b)c(b)"$ or	DERWENT;	
		"si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or	IBM_TDB	
		"si.b.c.1-b" or "si.1-b.c.b") near6 gate)		
	1	near12 x and (257/\$6.ccls. or 438/\$6.ccls.		
		or 361/\$6.ccls.)		
-	0	(("si.1-x. c.x." or "si.1-y. c.y." or	USPAT;	2002/05/10 18:35
		"si.x. c.1-x" or "si.y. c.1-y" or	US-PGPUB;	
		"si(x)c(1-x)" or "si(1-x)c(x)" or	EPO; JPO;	
1		"si(a)c(1-a)" or "si(b)c(1-b)" or	DERWENT;	
		"si(1-a)c(a)" or "si(1-b)c(b)" or	IBM_TDB	
		"si.a.c.1-a" or "si.1-a.c.a" or		
		"si.b.c.1-b" or "si.1-b.c.b") near12 gate)		
		near12 (x or y or a or b) and		
		(257/\$6.ccls. or 438/\$6.ccls. or		
1	1	361/\$6.ccls.)		L

"si.x.c.l-x" or "si.y. c.i-y" or US-PGPUB; EPO, JPO; "si(x)c(1-x)" or "si(hz)c(x)" or DERWENT; IBM_TDB "si.(x)c(1-x)" or "si.hz.c.a" or "si.h.c.l-x" or "si.h	_	1 1	(("si.1-x. c.x." or "si.1-y. c.y." or	USPAT;	2002/05/10 15:12
"si(a)c(1-a)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(1-a)c(a)" or "si(1-		1			1001,00,10 10:12
"si(a)c(1-a)" or "si(b)c(1-b)" or "si(a-b)c(a)" or "si(1-b)c(b)" or "si.a.c.l-a" or "si.d-b)c(b)" or "si.a.c.l-a" or "si.b.c.l-b" or "si.l-b.c.b") near12 gate) (silicon adj carbide or sic or "si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si(a)c(1-a)" or "si(a)c(1-b)" or "si(a)c(1-a)" or			"ai/y) a/1-y)" or "ai/1-y) a/y)" or		
"si(a-a)(a)" or "si(1-b)c(b)" or "si.a.c.1" or "si.a.c.1" or "si.b.a.c.1" or ") .
"si.h.a.c.l-a" or "si.l-a.c.a" or "si.h.c.l-b" or "si.l-b.c.b") nearl2 gate) "si.h.c.l-b" or "si.l-b.c.b") nearl2 gate) (silicon adj carbide or sic or "si.l-x. c.x." or "si.l-y.c.y." or "si.x.c.l-x" or "si.y.c.l-y" or "si(x)c(l-x)" or DERMENT; "si(b)c(l-b)" or "si.a.c.l-a" or "si.l-x.c.a" or "si.l-b.c.b") nearl2 gate "si.l-a.c.a" or "si.b.c.l-b" or "si.x.c.l-x" or "si.l-b.c.b") nearl2 gate (silicon adj carbide or sic or "si.l-x. c.x." or "si.l-y.c.y." or "si.x. c.l-x" or "si.l-b.c.b") nearl2 gate (silicon adj carbide or sic or "si.l-x. c.x." or "si.l-y.c.y." or "si.x. c.l-x" or "si.l-y.c.y." or "si.x. c.l-x" or "si.l-y.c.y." or "si.x. c.l-x" or "si.l-b.c.b") or "si.(l-a)c(a)" or "si.l-b.c.b" or "si.(l-a)c(a)" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. "si.l-b.c.b") near6 gate) and 257/\$6.ccls. "si.l-b.c.b") near6 gate) and 257/\$6.ccls. "si.l-b.c.b") near6 gate) and 257/\$6.ccls. "si.l-b.c.b") near6 gate) and 257/\$6.ccls. "si.l-b.c.b") near6 gate) and 257/\$6.ccls. "si.l-b.c.b") near6 gate) and 257/\$6.ccls. "si.l-b.c.l-w" or "si.y.c.l-y" or "si.l-b.c.l-w" or "si.y.c.l-y" or "si.(a)c(l-a)" or "si.l-b.c.w") or "si.l-a.c.a" or "si.l-b.c.w") or "si.l-a.c.a" or "si.l-b.c.h") near6 gate) and 257/\$6.ccls. "si.l-a.c.a" or "s			"S1(a)C(1-a)" or "S1(b)C(1-b)" or		
- 884 (silicon adj carbide or sic or "si.1-b.c.") near12 gate) (silicon adj carbide or sic or "si.1-b.c.")				IBW_LDB	
G84					
C.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si(y) c(l-x)" or "si.l-x. c.x." or "si.b.c.l-b" or "si.l-x. c.x." or "si.b.c.l-a" or "si.l-x. c.x." or "si.y. c.l-y" or "si(x) c(l-x)" or "si.y. c.l-x" or "si(x) c(l-x)" or "si.y. c.l-x" or "si.l-x. c.x." or "si.a) c(l-a)" or "si.l-a.c.a" or "si.l-a.c.a" or "si.l-a.c.a" or "si.l-a.c.a" or "si.l-a.c.a" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. - 2 ("6031263").PN. - 2 ("6049110").PN. - 2 ("6049110").PN. - 3 ("6049110").PN. - 4 ("6049110").PN. - 5 ("6049110").PN. - 5 ("6049110").PN. - 6 ("si.l-x. c.x." or "si.l-y. c.y." or "si.y. c.l-y" or "si.(a) c(l-a)" or "si.(a) c(l-a)" or "si.(a) c(l-b)" or "si.(a) c(l-a)" or "si.(a) c(l-b)" or "si.(a) c(l-a)"			"si.b.c.1-b" or "si.1-b.c.b") near12 gate)		
C.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si(x)c(l-x)" or "si.y. c.l-y" or "si.y. c.l-x" or "si.y. c.l-y" or "si.y. c.l-x" or "si.l-x. c.x." or "si.l-x. c.x." or "si.l-x. c.y." or "si.x. c.l-x" or "si.l-x. c.x." or "si.l-x. c.x." or "si.y. c.l-y" or "si.x. c.l-x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.l-x. c.x." or "si.y. c.l-y" or "si.x. c.l-x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.l-x. c.x." or "si.y. c.l-y" or "si.x. c.l-x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.l-x. c.x." or "si.l-x. c.x." or "si.x. c.l-x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.l-x. c.x." or "si.x. c.l-x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.l-x. c.x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.l-x. c.x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.l-x. c.x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.l-x. c.x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.l-x. c.x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.l-x. c.x" or "	-	684	(silicon adj carbide or sic or "si.1-x.	USPAT;	2002/05/10 15:13
or "si.y. c.l-y" or "si(x)c(l-x)" or DERWENT; si(1-x)c(x)" or "si(a)c(l-a)" or DERWENT; si(b)c(l-b)" or "si(a)c(l-a)" or DERWENT; si(b)c(l-b)" or "si(a)c.l-a" or "si(b)c(l-b)" or "si.a.c.l-a" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.c.l-x" or "si.c.l-x" or "si.c.l-a" or "si.c.l-a" or "si.c.l-a" or "si.c.l-a" or "si.c.l-a" or "si.c.l-a" or "si.c.l-b)c(b)" or "si.a.c.l-a" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-a.c.a" or "si.b.c.l-b" or "si.c.l-a" or "si.b.c.l-b" or "si.c.l-a" or			c.x." or "si.1-v. c.v." or "si.x. c.1-x"	US-PGPUB;	
"si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(b)c(a)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si(a)c(1-a)" or "si(1-a)c(a)" or "si(1-a)c(a)" or "si(1-a)c(a)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(x)c(1-x)" or "si(x)c(1-x)" or "si(b)c(1-b)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(a)c(1-a)" or "si(1-b)c(b)" or "si(a)c(1-a)" or "si(1-a)c(a)" or "si(1-a)					
"si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-b.c.a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-a.c.a" or "si.1-b.c.b") nearl2 gate ((silicon ad) carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "six.x. c.1-x" USPAT; US-PGPUB; cor "si.y. c.1-y" or "si.y. col-y" or "si.a.c.1-a" or "si.a.c.1-a" or "si.1-a.c.a" or "si.a.c.1-a" or "si.1-a.c.a" or "					1
"si(1-b)c(b)" or "si.a.c.1-a" or "si.1-b.c.a" or "si.b.c.1-b" or "si.1-b.c.b") nearl2 gate ((silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x.c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(b)c(1-b)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si.1-a.c.a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. 2 ("6249020").PN. USPAT; US-PGPUB; EPP, JPO; DERMENT; IBM_TDB					
- 161 (sil-a.c.a" or "si.b.c.l-b" or "si.l-a.c.a" or "si.l-a.c	ļ			TDM_IDD	
"si.1-b.c.b") nearl2 gate					
161			si.1-a.c.a" or "si.b.c.l-b" or		
C.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si.y. c.l-x" or "si.y. c.l-y" or "si.y. c.l-x" or "si.y. c.l-x" or "si.(l-x) c(x)" or "si.(l-x) c(x)" or "si.(l-a) c(a)" or "si.(l-b) c(b)" or "si.(l-a) c(a)" or "si.l-a.c.a" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. - 2 ("6049020").PN. - 2 ("6031263").PN. - 2 ("6049110").PN. - 3 ("6049110").PN. - 4 ("6049110").PN. - 5 ("6049110").PN. - 5 ("6049110").PN. - 6 (("si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.(l-a)c(a)" or "si.(l-b)c(b)" or "si.a.c.l-a" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. - 6 (("si.l-x. c.x." or "si.l-y. c.y." or "si.a.c.l-a" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. - 7 ("si.x. c.l-x" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. - 8 (("si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. - 9 (("si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. - 10 (("si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. - 11			"si.1-b.c.b") near12 gate	1	
or "si.y. c.l-y" or "si(x)c(l-x)" or "si(1-x)c(x)" or "si(1-x)c(x)" or "si(a)c(l-a)" or "si(1-x)c(x)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.l-a" or "si.1-a.c.a" or "si.1-a.c.a" or "si.1-a.c.a" or "si.1-a.c.b") near6 gate) and 257/\$6.ccls. - 2 ("6249020").PN. - 2 ("6031263").PN. - 2 ("6049110").PN. - 3 ("6049110").PN. - 4 ("6049110").PN. - 5 ("6049110").PN. - 5 ("6049110").PN. - 6 ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.y. c.l-y" or "si.l-a.c.a" or "si.l-a.c.a" or "si.b.c.l-a" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-a.c.a" or "si.x. c.l-a" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. - 6 ("si.1-x. c.x." or "si.1-y. c.y." or "si.b.c.l-b" or "si.b.c.l-b" or "si.l-a.c.a" or "	-	161	((silicon adj carbide or sic or "si.1-x.	USPAT;	2002/05/10 18:42
or "si.y. c.l-y" or "si(x)c(l-x)" or "si(1-x)c(x)" or "si(1-x)c(x)" or "si(a)c(l-a)" or "si(1-x)c(x)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.l-a" or "si.1-a.c.a" or "si.1-a.c.a" or "si.1-a.c.a" or "si.1-a.c.b") near6 gate) and 257/\$6.ccls. - 2 ("6249020").PN. - 2 ("6031263").PN. - 2 ("6049110").PN. - 3 ("6049110").PN. - 4 ("6049110").PN. - 5 ("6049110").PN. - 5 ("6049110").PN. - 6 ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.y. c.l-y" or "si.l-a.c.a" or "si.l-a.c.a" or "si.b.c.l-a" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-a.c.a" or "si.x. c.l-a" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. - 6 ("si.1-x. c.x." or "si.1-y. c.y." or "si.b.c.l-b" or "si.b.c.l-b" or "si.l-a.c.a" or "			c.x." or "si.1-v. c.v." or "si.x. c.1-x"	US-PGPUB;	
"si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si.1-a)c(a)" or "si.1-a.c.a" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls.				EPO: JPO:	
"si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.b.c.1-b" or "si.a.c.1-a" or "si.b.c.b") near6 gate) and 257/\$6.ccls. 2 ("6031263").PN. 2 ("6031263").PN. 3 ("6031263").PN. 4 ("6031263").PN. 5 ("6049110").PN. 5 ("6049110").PN. 5 ("6049110").PN. 6 (("si.1-x. c.x." or "si.1-y. c.y." or US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB US-PGPUB; EPO					!
"si(1-b)c(b)" or "si.a.c.l-a" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. ("6249020").PN. 2 ("6031263").PN. 2 ("6049110").PN. 2 ("6049110").PN. 3 ("6049110").PN. 4 ("si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si(a)c(l-a)" or "si(l-b)c(b)" or "si.a.c.l-a" or "si.l-y. c.y." or "si.x. c.l-x" or "si.l-y. c.y." or "si.a.c.l-a" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. (("si.l-x. c.x." or "si.l-y. c.y." or "si.a.c.l-a" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. (("si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.l-y. c.y." or "si.a.c.l-a" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. (("si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x"					
- 2 ("6031263").PN. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; USP				1 TPM_1 DP	
- 2 ("6249020").PN. - 2 ("6031263").PN. - 2 ("6031263").PN. - 2 ("6049110").PN. - 2 ("6049110").PN. - 3 ("61.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.(1-x) c(x)" or "si.(1-a) c(a)" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. - 0 (("si.1-x. c.x." or "si.1-y. c.y." or "si.2-d.c.a" or "si.x. c.1-x" or "si.y. c.1-y" or "si.a.c.1-a" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. - 0 (("si.1-x. c.x." or "si.1-y. c.y." or "si.2-d.c.a" or "si.x. c.1-x" or "si.y. c.1-y" or "si.a.c.1-a" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. - 0 (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si.y. c.1					
- 2 ("6249020").PN. - 2 ("6031263").PN. - 2 ("6031263").PN. - 2 ("6049110").PN. - 2 ("6049110").PN. - 3 ("6049110").PN. - 4 ("5i.1-x. c.x." or "si.1-y. c.y." or USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; USPĀT; USPĀT JPO;					
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; USP					
- 2 ("6031263").PN.	-	2	("6249020").PN.	USPAT;	2002/05/10 16:24
DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB				US-PGPUB;	
DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB				EPO: JPO:	
- 2 ("6031263").PN. IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; US-PGPUB;	l				
- 2 ("6031263").PN.				1	
US-PGPUB; EPO; JPO; DERWENT; IBM TDB USFAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USFAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USFAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; U		2	("6021262") DN	}	2002/05/10 17:09
- 2 ("6049110").PN. - 2 ("6049110").PN. - 3 ("si.1-x. c.x." or "si.1-y. c.y." or USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB "si.x. c.1-x" or "si.y. c.1-y" or USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB "si.x. c.1-x" or "si.y. c.1-y" or USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB "si(a)c(1-a)" or "si(1-b)c(b)" or USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 4 ("si.1-x. c.x." or "si.1-a.c.a" or "si.b.c.1-b" or "si.b.c.1-b" or "si.1-a.c.a" or "si.y. c.1-y" or USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB - 5 ("si.1-x. c.x." or "si.1-y. c.y." or USPAT; US-PGPUB; US-P	-	2	("0031203).PN.	,	2002/03/10 17:09
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB OUSPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB DERWENT; IBM_TDB				1	
- 2 ("6049110").PN. IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; "si(x)c(1-x)" or "si(b)c(1-b)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. O ("si.1-x. c.x." or "si.1-y. c.y." or "si.2-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si.y. c	1			1	İ
- 2 ("6049110").PN. USPĀT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB (("si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si(x)c(l-x)" or "si(l-x)c(x)" or "si(a)c(l-a)" or "si(b)c(l-b)" or "si.a.c.l-a" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls. (("si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si.x. c.l-x" or "si.y. c.l-y" or "si(x)c(l-x)" or "si(l-x)c(x)" or "si(a)c(l-a)" or "si(l-x)c(x)" or "si(a)c(l-a)" or "si(l-b)c(b)" or "si(a)c(l-a)" or "si(l-b)c(b)" or "si.a.c.l-a" or "si.l-a.c.a" or "si.a.c.l-a" or "si.l-a.c.a" or "si.a.c.l-a" or "si.l-a.c.a" or				DERWENT;	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(a)c(1-x)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si				IBM_TDB	
- 0 (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(1-a)c(a)" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. - 0 (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(1-a)c(a)" or "si(1-x)c(x)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si(1-a)c(a)" or "si(1-a)c(a)" or "si(1-a)c(a)" or "si.1-a.c.a" or "si.a.c.1-a" or "si.1-a.c.a" or "si.1	_	2	("6049110").PN.	USPAT;	2002/05/10 17:09
- 0 (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(1-a)c(a)" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. - 0 (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(1-a)c(a)" or "si(1-x)c(x)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si(1-a)c(a)" or "si(1-a)c(a)" or "si(1-a)c(a)" or "si.1-a.c.a" or "si.a.c.1-a" or "si.1-a.c.a" or "si.1				US-PGPUB;	
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB				•	
- 0 (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. 0 (("si.1-x. c.x." or "si.y. c.1-y" or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(b)c(1-b)" or "si(x)c(1-x)" or "si(1-b)c(b)" or "si(x)c(1-x)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si				1	
- 0 (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. 0 (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(x)c(1-x)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si(1-a)c(a)" or "si(1-a)c(a)" or "si(1-a)c(a)" or "si.1-a.c.a"					
"si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si.x. c.1-x" or "si(1-x)c(x)" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or				_	2002/05/10 10:22
"si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.a.c.1-a" or "si.1-a.c.a" or	-	0	(("si.1-x. c.x." or "si.1-y. c.y." or		2002/05/10 18:33
"si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or				1	
"si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or			"si(x)c(1-x)" or $"si(1-x)c(x)"$ or	EPO; JPO;	
"si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or			"si(a)c(1-a)" or "si(b)c(1-b)" or	DERWENT;	
"si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or			"si(1-a)c(a)" or "si(1-b)c(b)" or	IBM TDB	
"si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or				_	
and 257/\$6.ccls. (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(1-x)c(x)" or "si(1-x)c(x)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si.1-a.c.a" or "si.1-a.c.a" or "si.1-a.c.a" or "si.1-a.c.a" or					
O (("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si() c(1-x)" or "si(1-x)c(x)" or "si() c(1-a)" or "si(1-b)c(b)" or "si(1-a)c(a)" or "si.1-a.c.a" or	İ				
"si.x. c.1-x" or "si.y. c.1-y" or				HCDAT.	2002/05/10 10:22
"si(x)c(1-x)" or "si(1-x)c(x)" or	-			1	2002/03/10 10:33
"si(a)c(1-a)" or "si(b)c(1-b)" or DERWENT; "si(1-a)c(a)" or "si(1-b)c(b)" or IBM_TDB "si.a.c.1-a" or "si.1-a.c.a" or	1				
"si(1-a)c(a)" or "si(1-b)c(b)" or IBM_TDB "si.a.c.1-a" or "si.1-a.c.a" or	1				
"si.a.c.1-a" or "si.1-a.c.a" or	}			DERWENT;	
"si.a.c.1-a" or "si.1-a.c.a" or	ļ		"si(1-a)c(a)" or "si(1-b)c(b)" or	IBM TDB	
"si.b.c.1-b" or "si.1-b.c.b") near6 gate)]		"si.a.c.1-a" or "si.1-a.c.a" or	-	
			"si.b.c.1-b" or "si.1-b.c.b") near6 gate)		

			1	
-	51	(US-5451798-\$ or US-6166319-\$ or	USPAT;	2002/05/10 18:34
		US-4113515-\$ or US-4473836-\$ or	US-PGPUB;	
		US-5698869-\$ or US-5858811-\$ or	EPO; JPO;	
		US-5976926-\$ or US-6031263-\$ or	DERWENT	
		US-6084248-\$ or US-6093937-\$ or		
		US-6099574-\$ or US-6130147-\$ or]	
		US-6144581-\$ or US-6163066-\$ or		
		US-6166401-\$ or US-5661312-\$ or		
		US-5719410-\$ or US-5798548-\$ or		
		US-5801401-\$ or US-6011279-\$ or		
		US-6049110-\$ or US-6306691-\$ or	1	
		US-6313482-\$ or US-6365919-\$ or		
ļ		US-6249020-\$ or US-6344663-\$).did. or		
[(US-5886368-\$ or US-6383576-\$ or		1
		US-4826778-\$ or US-5039354-\$ or		
		US-5056897-\$ or US-5159424-\$ or		1
		US-5260560-\$ or US-5369040-\$).did. or		
		(US-20010032997-\$ or		1
		US-20010049183-\$).did. or (EP-681333-\$ or		
		EP-291951-\$).did. or (JP-04056769-\$ or		
İ		JP-62122275-\$ or JP-63181473-\$ or		
		JP-01115162-\$ or JP-63219172-\$ or		
İ		JP-63289960-\$ or JP-56056677-\$).did. or	1	
		(JP-04056769-\$ or JP-62122275-\$ or		
		EP-276002-\$ or EP-291951-\$ or		
{		JP-01115162-\$ or JP-07115191-\$).did.		
-	351	silicon near3 doped near6 carbon	USPAT;	2002/05/10 18:36
1			US-PGPUB;	1
į			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
_	45	(silicon near3 doped near6 carbon) and	USPAT;	2002/05/10 18:38
	1	(257/\$6.ccls. or 438/\$6.ccls.) and gate	US-PGPUB;	2002, 00, 10 10:00
	İ	(257) \$0.0013. Of 450) \$0.0013.) and gate	EPO; JPO;	
	}		DERWENT;	
			[
		(/	IBM TDB	2002/05/10 10 40
-	4	((silicon near3 doped near6 carbon) near12	USPAT;	2002/05/10 18:40
		gate) and (257/\$6.ccls. or 438/\$6.ccls.)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5	((silicon near3 dop\$3 near6 carbon) near12	USPAT;	2002/05/10 18:41
		gate) and (257/\$6.ccls. or 438/\$6.ccls.)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	235	((carbon or silicon adj carbide or sic or	USPĀT;	2002/05/10 18:43
1		"si.1-x. c.x." or "si.1-y. c.y." or "si.x.	US-PGPUB;	
		c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)"	EPO; JPO;	1
		or "si(1-x)c(x)" or "si(a)c(1-a)" or	DERWENT;	1
		"si(b)c(1-b)" or $"si(1-a)c(a)"$ or	IBM TDB	1
		$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	12.1-122	1
				1
		"si.1-a.c.a" or "si.b.c.1-b" or		
		"si.1-b.c.b") near6 gate) and 257/\$6.ccls.	LIGDAE	2000/05/10 00 10
_	74	(((carbon or silicon adj carbide or sic or	USPAT;	2002/05/10 20:13
		"si.1-x. c.x." or "si.1-y. c.y." or "si.x.	US-PGPUB;	
		c.1-x" or "si.y. $c.1-y"$ or "si(x)c(1-x)"	EPO; JPO;	
		or "si(1-x)c(x)" or "si(a)c(1-a)" or	DERWENT;	†
		"si(b)c(1-b)" or "si(1-a)c(a)" or	IBM_TDB	
		"si(1-b)c(b)" or "si.a.c.1-a" or		1
		"si.1-a.c.a" or "si.b.c.1-b" or		1
		"si.1-b.c.b") near6 gate) and		
		257/\$6.ccls.) not (((silicon adj carbide		1
]	or sic or "si.1-x. c.x." or "si.1-y. c.y."		1
		or "si.x. c.1-x" or "si.y. c.1-y" or		1
		"si(x)c(1-x)" or "si(1-x)c(x)" or		
		"si(a)c(1-a)" or "si(b)c(1-b)" or		
		"si(1-a)c(a)" or $"si(1-b)c(b)"$ or		!
]	"si.a.c.1-a" or "si.1-a.c.a" or		
		"si.b.c.1-b" or "si.1-b.c.b") near6 gate)		
		and 257/\$6.ccls.)		
	ı	and 20//40.0015.)	l	

_	0	silicon-doped adj carbon adj (film or	USPAT;	2002/05/10 20:13
		electrode)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	į
			IBM_TDB	0000/05/00 00
-	0		USPAT;	2002/05/10 20:14
	1	electrode)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		1	IBM_TDB	0000/05/00 00 15
] -	201	((c or carbon) near (si or silicon)) adj	USPAT;	2002/05/10 20:15
1	l	(film or electrode)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
	10092	((c or carbon) near6 (si or silicon))	USPAT;	2002/05/10 20:16
-	10092	near6 (film or electrode)	US-PGPUB;	2002/03/10 20:16
	j	Heart (IIIM Of electione)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	3434	(carbon near6 (si or silicon)) near6 (film	USPAT;	2002/05/10 20:16
	3131	or electrode)	US-PGPUB;	2002/03/10 20:10
		01 01001000/	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	118	(carbon near1 (si or silicon)) near3 (film	USPAT;	2002/05/10 21:21
		or electrode) and (257/\$6.ccls. or	US-PGPUB;	· · · - · - · - · - · ·
		438/\$6.ccls.)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	polysilicon/carbon near12 gate adj	USPAT;	2002/05/10 21:22
		electrode	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/05/40 04 00
-	0	"polysilicon/carbon" near12 gate adj	USPAT;	2002/05/10 21:22
1		electrode	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	l 0	(polysilicon near1 carbon) near12 gate adj	USPAT;	2002/05/10 21:23
		electrode	US-PGPUB;	2002, 00, 10 21.20
			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	1	(silicon nearl carbon) near12 gate adj	USPĀT;	2002/05/10 21:49
		electrode	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	6	p-doped adj silicon adj carbide	USPAT;	2002/05/10 21:30
			US-PGPUB;	
			EPO; JPO;	
]			DERWENT;	
	_	D depent needla	IBM_TDB	2002/05/12 21
-	7	P-dopant near12 carbon	USPAT;	2002/05/10 21:49
1			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	o	carbon adj doping adj2 silicon adj carbide	USPAT;	2002/05/11 16:21
		carson adj dopring adje stricon adj carbide	US-PGPUB;	2002/00/11 10.21
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	4	silicon adj doping adj2 carbon	USPAT;	2002/05/11 16:27
			US-PGPUB;	
			EPO; JPO;	
ļ l			DERWENT;	
	L		IBM TDB	

-	0	p-doped adj silicon adj carbon	USPAT;	2002/05/11 16:27
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	7	p-doped adj2 silicon adj2 carbon	USPAT;	2002/05/11 16:28
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/05/11 16 31
-	1	11 1 1 1 1 1 1 1 1	USPAT; US-PGPUB;	2002/05/11 16:31
		carbon	EPO; JPO;	,
			DERWENT;	
			IBM TDB	
_	0	"si.sub.1-x.c.sub.x"	USPAT;	2002/05/11 16:35
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		 "si.sub.1-x c.sub.x"	IBM_TDB USPAT;	2002/05/11 16:43
-	57	51.5UD.1-X C.5UD.X	US-PGPUB;	2002/03/11 10:43
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0		USPĀT;	2002/05/11 16:43
		function or workfunction)	US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
	2	"si.sub.1-x c.sub.x" near20 (barrier or	IBM_TDB USPAT;	2002/05/11 16:48
-	2	work adj function or workfunction)	US-PGPUB;	2002/03/11 10.40
		work day randeron or workranderon,	EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
_	1	"si.sub.x c.sub.1-x" near20 (barrier or	USPAT;	2002/05/11 16:49
		work adj function or workfunction)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	10	"si.sub.1-x c.sub.x" near20 (electrode or	USPAT;	2002/05/11 17:04
		conductivity or conduction)	US-PGPUB;	
		· ·	EPO; JPO;	
	}		DERWENT;	
			IBM_TDB	0000/05/11 00 00
-	1	("si.sub.1-x c.sub.x" or "si.sub.x	USPAT;	2002/05/11 20:09
		c.sub.1-x" or "si.sub.1-y c.sub.y" or "si.sub.y c.sub.1-y") near20 electron adj	US-PGPUB; EPO; JPO;	
		affinity	DERWENT;	
			IBM TDB	
_	0	resistivity near4 "si.sub.1-x. c.x"	USPĀT;	2002/05/11 20:26
			US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
_	965	(conductivity or registivity) pearl?	IBM_TDB USPAT;	2002/05/11 20:39
-	903	(conductivity or resistivity) near12 silicon adj carbide	US-PGPUB;	2002/03/11 20:39
	1	outstac	EPO; JPO;	
]	1		DERWENT;	
1			IBM_TDB	
-	0	(conductivity or resistivity) near12	USPĀT;	2002/05/11 21:10
		"si.sub.1-x c.x"	US-PGPUB;	
	1		EPO; JPO;	,
	1		DERWENT; IBM TDB	
_	8	 barrier adj energy near12 silicon adj	USPAT;	2002/05/11 21:14
		dioxide	US-PGPUB;	
			EPO; JPO;	
	İ		DERWENT;	
			IBM TDB	

_	0	barrier adj energy near12 silicon adj carbide	USPAT; US-PGPUB;	2002/05/11 21:20
			EPO; JPO; DERWENT;	
_	108	barrier adj energy.ti,ab.	IBM_TDB USPAT;	2002/05/11 21:23
			US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	
-	2		USPĀT;	2002/05/11 21:24
		"si.sub.1-x. c.x" or silicon adj carbide)	US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	
-	21	<pre>(resistivity or conductivity) near12 (silicon adj carbide or "si.sub.1-x.</pre>	USPAT; US-PGPUB;	2002/05/12 12:26
		c.sub.x" or "si.sub.x. c.sub.1-x") near12	EPO; JPO;	
		×	DERWENT; IBM_TDB	
-	17	barrier adj energy near12 gate near12 insulator	USPAT; US-PGPUB;	2002/05/12 12:07
ĺ			EPO; JPO; DERWENT;	
_	3	("5661312").PN.	IBM_TDB USPAT;	2002/05/12 12:10
		(3001312).IN.	US-PGPUB;	2002/03/12 12.10
			EPO; JPO; DERWENT;	
_	0	("floating adj gate and control adj gate	IBM_TDB USPAT;	2002/05/12 12:10
		and silicon adj dioxide and (sic or silicon adj carbide)").PN.	US-PGPUB; EPO; JPO;	
		, , , , , , , , , , , , , , , , , , , ,	DERWENT; IBM TDB	
_	30		USPĀT;	2002/05/12 12:11
		silicon adj dioxide and (sic or silicon adj carbide)	US-PGPUB; EPO; JPO;	
ē			DERWENT; IBM TDB	
_	0	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon	USPAT; US-PGPUB;	2002/05/12 12:12
		adj carbide) and photodetection	EPO; JPO; DERWENT;	
	20		IBM TDB	2000/05/10 10 01
_	30	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon	USPAT; US-PGPUB;	2002/05/12 12:21
i		adj carbide) and memory	EPO; JPO; DERWENT;	
_	18	floating adj gate and control adj gate and	IBM_TDB USPAT;	2002/05/12 12:21
		silicon adj dioxide and (sic or silicon adj carbide) and memory and barrier	US-PGPUB; EPO; JPO;	
		and buttlet	DERWENT; IBM TDB	
-	18		USPĀT;	2002/05/12 12:23
		silicon adj dioxide and (sic or silicon adj carbide) and memory and (barrier adj	US-PGPUB; EPO; JPO;	
		energy or potential adj barrier or tunneling adj barrier or interface adj	DERWENT; IBM_TDB	
_	3	barrier or barrier) ("5886368").PN.	USPAT;	2002/05/12 17:44
			US-PGPUB; EPO; JPO;	
			DERWENT;	
_	3	("5661312").PN.	IBM_TDB USPAT;	2002/05/12 17:46
			US-PGPUB; EPO; JPO;	
-			DERWENT; IBM TDB	

-	46061	polycrystalline near12 silicon carbide and	USPAT;	2002/05/12 17:48
		(mosfet or fet or nmosfet or pmosfet or	US-PGPUB; EPO; JPO;	
		cmosfet or field ajd effect adj transistor) and (memory or photodetect\$3)	DERWENT;	
		Clansistor, and (memory or photodececes)	IBM TDB	
_	13	polycrystalline near12 silicon adj carbide	USPĀT;	2002/05/12 17:50
		and (mosfet or fet or nmosfet or pmosfet	US-PGPUB;	
		or cmosfet or field ajd effect adj	EPO; JPO;	
		transistor) and (memory or photodetect\$3)	DERWENT;	
		(1	IBM_TDB USPAT;	2002/05/12 17:51
-	22	(polycrystalline or monocrystalline) near12 silicon adj carbide and (mosfet or	US-PGPUB;	2002/03/12 17:31
		fet or nmosfet or pmosfet or cmosfet or	EPO; JPO;	
		field ajd effect adj transistor) and	DERWENT;	
		(memory or photodetect\$3)	IBM_TDB	
_	4		USPAT;	2002/05/12 17:52
		near12 silicon adj carbide near12 gate and	US-PGPUB;	
		(mosfet or fet or nmosfet or pmosfet or	EPO; JPO; DERWENT;	
		cmosfet or field ajd effect adj transistor) and (memory or photodetect\$3)	IBM TDB	
_	24		USPAT;	2002/05/12 18:16
1		near12 silicon adj carbide near12 gate	US-PGPUB;	111, 30, 12 10.10
1			EPO; JPO;	
			DERWENT;	
	_	(#5250040#) 577	IBM_TDB	0000/05/10 10 55
-	3	("5369040").PN.	USPAT; US-PGPUB;	2002/05/12 18:17
			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
1 -	10		USPĀT;	2002/05/12 18:30
		and photodetect\$3 and (mosfet or cmos or	US-PGPUB;	
		cmosfet or nmos or nmosfet or pmos or	EPO; JPO;	
		pmosfet or transistor or field adj effect)	DERWENT; IBM TDB	
_	0	 floating adj gate near12 control adj gate	USPAT;	2002/05/12 18:31
		near12 silicon adj carbide and	US-PGPUB;	2002/03/12 10:31
		photodetect\$3 and (mosfet or cmos or	EPO; JPO;	
		cmosfet or nmos or nmosfet or pmos or	DERWENT;	
		pmosfet or transistor or field adj effect)	IBM_TDB	0000/05/10 10 01
-	0	floating adj gate near12 control adj gate	USPAT;	2002/05/12 18:31
		near12 silicon adj carbide and photodetect\$3	US-PGPUB; EPO; JPO;	
		photodetectys	DERWENT;	
	1		IBM TDB	
-	0	floating adj gate near12 control adj gate	USPĀT;	2002/05/12 18:32
1	1	near12 silicon adj carbide	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
l _	2	floating adj gate near12 control adj gate	USPAT;	2002/05/12 18:56
		near12 (sic or silicon adj carbide or	US-PGPUB;	
1		"si.sub.1-x. c.sub.x")	EPO; JPO;	
			DERWENT;	
	_	(#5000050#) 799	IBM_TDB	0000/05/10 10 55
-	2	("5989958").PN.	USPAT;	2002/05/12 19:00
			US-PGPUB; EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	3	("5801401").PN.	USPĀT;	2002/05/12 19:33
			US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
_	2	("5808336").PN.	IBM_TDB USPAT;	2002/05/12 19:43
	2	0000000 /	US-PGPUB;	2002,00,12 13.43
	1		EPO; JPO;	
		•	DERWENT;	
			IBM_TDB	

			TIODAM.	1 2002 /05 /10 10 42
-	3	("5801401").PN.	USPAT; US-PGPUB;	2002/05/12 19:43
			EPO; JPO;	
			DERWENT;	
			IBM TDB	1
	3	("4473836").PN.	USPAT;	2002/05/13 10:06
-	3	("44/3836").PN.	US-PGPUB;	2002/03/13 10.06
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
_	2	("5808336").PN.	USPAT;	2002/05/13 10:11
		(5000555	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	3	("5801401").PN.	USPĀT;	2002/05/13 11:25
		(0002002	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0		USPAT;	2002/05/13 11:26
		source same drain and silcion adj carbide	US-PGPUB;	
		and silicon adj substrate and channel	EPO; JPO;	
		-	DERWENT;	
Į.			IBM_TDB	
_	41	floating adj gate and control adj gate and	USPĀT;	2002/05/13 11:27
ļ		source same drain and silicon adj carbide	US-PGPUB;	
1		and silicon adj substrate and channel	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	41	floating adj gate and control adj gate and	USPAT;	2002/05/13 12:16
		source same drain and silicon adj carbide	US-PGPUB;	
		and silicon adj substrate and channel and	EPO; JPO;	
		(memory or photodetect\$3)	DERWENT;	
		10.61	IBM_TDB	2002/05/12 12:15
_	74	crystalline near12 floating adj gate	USPAT;	2002/05/13 12:16
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
	37	crystalline near3 floating adj gate	USPAT;	2002/05/13 13:21
_	3/	crystarrine hears rroating adj gate	US-PGPUB;	2002/03/13 13.21
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	5	(("5661312") or ("5798548") or ("5989958")	USPAT	2002/05/13 16:23
		or ("5369040") or ("5557122")).PN.		
_	47	hamakawa.in. and carbide	USPAT;	2002/05/13 16:13
	1		US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	24	hamakawa.in. and carbide	JPO_	2002/05/13 16:13
		("5808336").PN.	USPAT	2002/05/13 17:16

	T = 0	1 / (NAA CO CZON) (NAA CO ZOZON) (NAE OZ CZON)	Licoam	2002/05/12 17:20
-	52	(("4460670") or ("4462150") or ("4507673")	USPAT	2002/05/13 17:30
		or ("4657699") or ("4738729") or		
		("4768072") or ("4769686") or ("4841349")		
		or ("4849797") or ("4893273") or		
		("5049950") or ("5111430") or ("5145741")		
		or ("5235195") or ("5260593") or		
ı		("5293560") or ("5298796") or ("5369040")		
		or ("5371383") or ("5407845") or		
		("5415126") or ("5449941") or ("5455432")		
		or ("5465249") or ("5477485") or		
		("5508543") or ("5530581") or ("5557114")		
1		or ("5562769") or ("5580380") or		
		("5604357") or ("5623442") or ("5629222")		
		or ("5654208") or ("5670790") or		
		("5714766") or ("5719410") or ("5740104")		
		or ("5754477") or ("5786250") or		
		("5789276") or ("5801401") or ("5846859")		
		or ("5877041") or ("5886368") or		
		("5886379") or ("5898197") or ("5907775")		
		or ("6018166") or ("6031263") or		İ
		("6034001") or ("6075259")).PN.		
_	6	((("4460670") or ("4462150") or	USPAT;	2002/05/13 18:18
		("4507673") or ("4657699") or ("4738729")	US-PGPUB;	
		or ("4768072") or ("4769686") or	EPO; JPO;	
		("4841349") or ("4849797") or ("4893273")	DERWENT;	
		or ("5049950") or ("5111430") or	IBM TDB	
		("5145741") or ("5235195") or ("5260593")		
		or ("5293560") or ("5298796") or		
		("5369040") or ("5371383") or ("5407845")		ļ
		or ("5415126") or ("5449941") or	ļ	
	Ì	("5455432") or ("5465249") or ("5477485")		
		or ("5508543") or ("5530581") or	1	į
		("5557114") or ("5562769") or ("5580380")		
		or ("5604357") or ("5623442") or		İ
		("5629222") or ("5654208") or ("5670790")		i
		or ("5714766") or ("5719410") or		
		("5740104") or ("5754477") or ("5786250")		
		or ("5789276") or ("5801401") or		
		("5846859") or ("5877041") or ("5886368")		
		or ("5886379") or ("5898197") or		
		("5907775") or ("6018166") or ("6031263")		
		or ("6034001") or ("6075259")).PN.) and		
		("si.sub.1-x. c.sub.x" or "si.sub.1-y.		
		c.sub.y" or "si.sub.x c.sub.1-x" or		
ĺ		"si.sub.y c.sub.1-y" or silicon carbide or		
		sic) and source and drain and floating adj		
		gate and control adj gate and silicon adj		
		dioxide	!	

_	0	((("4460670") or ("4462150") or	USPAT;	2002/05/13 20:34
		("4507673") or ("4657699") or ("4738729")	US-PGPUB;	
		or ("4768072") or ("4769686") or	EPO; JPO;	
		("4841349") or ("4849797") or ("4893273")	DERWENT;	
		or ("5049950") or ("5111430") or	IBM TDB	l f
		("5145741") or ("5235195") or ("5260593")	_	
		or ("5293560") or ("5298796") or		
		("5369040") or ("5371383") or ("5407845")		
		or ("5415126") or ("5449941") or		
		("5455432") or ("5465249") or ("5477485")		
		or ("5508543") or ("5530581") or		
		("5557114") or ("5562769") or ("5580380")		
		or ("5604357") or ("5623442") or		
		("5629222") or ("5654208") or ("5670790")		
		or ("5714766") or ("5719410") or		
		("5740104") or ("5754477") or ("5786250")		
		or ("5789276") or ("5801401") or		
		("5846859") or ("5877041") or ("5886368")		
		or ("5886379") or ("5898197") or		
		("5907775") or ("6018166") or ("6031263")		
		or ("6034001") or ("6075259")).PN.) and		
		("si.sub.1-x. c.sub.x" or "si.sub.1-y.		
		c.sub.y" or "si.sub.x c.sub.1-x" or		
		"si.sub.y c.sub.1-y") and source and drain		
	ł	and floating adj gate and control adj gate		
		and floating adj gate and control adj gate and silicon adj dioxide		
	588	(257/77).CCLS.	USPAT;	2002/05/13 20:34
-	700	(237777).CCL3.	US-PGPUB	2002/03/13 20:34
	118	(257/153).CCLS.	USPAT;	2002/05/13 20:34
-	110	(237/133).CCLS.	US-PGPUB	2002/03/13 20:34
	402	(257/314).CCLS.		2002/05/13 20:39
-	402	(257/314).CCLS.	USPAT;	2002/05/13 20:39
	700	(257/215) COLC	US-PGPUB	2002/05/12 20:20
<u> </u>	782	(257/315).CCLS.	USPAT;	2002/05/13 20:39
	043	(257 (216) COT 0	US-PGPUB	2002/05/12 20 40
_	943	(257/316).CCLS.	USPAT;	2002/05/13 20:40
	2211	//057/77) COT 0) //057/153) COT 0)	US-PGPUB	2000/05/12 00 40
-	2311	((257/77).CCLS.) or ((257/153).CCLS.) or	USPAT;	2002/05/13 20:40
		((257/314).CCLS.) or ((257/315).CCLS.) or	US-PGPUB;	
1		((257/316).CCLS.)	EPO; JPO;	
			DERWENT;	
	357	///257/77) COIC \ am //257/153\ COIC \	IBM TDB	2002/05/12 20 14
-	357	(((257/77).CCLS.) or ((257/153).CCLS.) or	USPAT;	2002/05/13 20:44
		((257/314).CCLS.) or ((257/315).CCLS.) or	US-PGPUB;	
		((257/316).CCLS.)) and silicon adj carbide	EPO; JPO;	
		·	DERWENT;	
	1	///053/33> 0010 > 55 //053/353> 0010 >	IBM_TDB	0000/05/10 01 10
-	90	(((257/77).CCLS.) or ((257/153).CCLS.) or	USPAT;	2002/05/13 21:12
		((257/314).CCLS.) or ((257/315).CCLS.) or	US-PGPUB;	
		((257/316).CCLS.)) and (silicon adj	EPO; JPO;	
		carbide near15 gate)	DERWENT;	
	_	(11500005011) 707	IBM_TDB	0000/05/50 05 55
-	2	("5989958").PN.	USPAT;	2002/05/13 21:12
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

	115	(US-5449941-\$ or US-5455432-\$ or	USPAT;	1 2002/05/14 08:24
-	113	US-5039354-\$ or US-5056897-\$ or	US-PGPUB;	2002/03/14 00:24
	1	US-5159424-\$ or US-5260560-\$ or	EPO; JPO;	
	ŀ	US-5369040-\$ or US-5451798-\$ or	DERWENT	
		· ·	DEKMENT	
	İ	US-5734181-\$ or US-6166319-\$ or		
		US-6383576-\$ or US-5801401-\$ or		
		US-5989958-\$ or US-6344663-\$ or		
		US-4113515-\$ or US-4473836-\$ or		
		US-5698869-\$ or US-5858811-\$ or		
		US-5976926-\$ or US-6031263-\$ or		
		US-6084248-\$ or US-6093937-\$ or		
		US-6099574-\$ or US-6130147-\$ or		
		US-6144581-\$ or US-6163066-\$).did. or		
		(US-6166401-\$ or US-5465249-\$ or		
1		US-4451391-\$ or US-6309907-\$ or		
ł		US-5061976-\$ or US-5625217-\$ or		
		US-5661312-\$ or US-5798548-\$ or		
		US-6011279-\$ or US-6049110-\$ or		
		US-6249020-\$ or US-6306691-\$ or		
		US-6313482-\$ or US-6365919-\$ or	1	
		US-5719410-\$ or US-5886368-\$ or		
		US-4826778-\$ or US-6351411-\$ or		
		US-5557114-\$ or US-5562769-\$ or		
		US-5580380-\$ or US-5604357-\$ or		
		US-5623442-\$ or US-5629222-\$ or		
		US-5654208-\$ or US-5670790-\$ or		
		US-5714766-\$).did. or (US-5740104-\$ or		
		US-5754477-\$ or US-5786250-\$ or		
		US-5789276-\$ or US-5846859-\$ or	Ì	
	i	US-5877041-\$ or US-5886379-\$ or		
		US-5907775-\$ or US-6018166-\$ or		
		US-6034001-\$ or US-6075259-\$ or		
		US-5557122-\$ or US-5866930-\$ or		+
		US-5898197-\$ or US-5808336-\$ or		
		US-5393999-\$ or US-5539217-\$ or		1
		US-4460670-\$ or US-4462150-\$ or		
		US-4507673-\$ or US-4657699-\$ or		
		US-4738729-\$ or US-4768072-\$ or		
		US-4769686-\$ or US-4841349-\$ or		
		US-4849797-\$ or US-4893273-\$).did. or		
		(US-5049950-\$ or US-5111430-\$ or		
		US-5145741-\$ or US-5235195-\$ or		
		US-5260593-\$ or US-5293560-\$ or		
		US-5298796-\$ or US-5371383-\$ or		1
		US-5407845-\$ or US-5415126-\$ or		†
		US-5508543-\$ or US-5530581-\$ or		
		US-5477485-\$).did. or (US-20010032997-\$ or		
		US-20010049183-\$ or US-20020024050-\$ or		
		US-20020017647-\$).did. or (EP-291951-\$ or		
		EP-681333-\$).did. or (JP-62122275-\$ or		
		JP-63181473-\$ or JP-01115162-\$ or		1
		JP-63219172-\$ or JP-04056769-\$ or		
		JP-63289960-\$ or JP-57126175-\$ or		1
		JP-04061170-\$ or JP-56056677-\$ or		,
		JP-02203564-\$).did. or (JP-04056769-\$ or		
		JP-62122275-\$ or JP-01115162-\$ or		
		EP-291951-\$ or EP-276002-\$ or		
		JP-07115191-\$).did.		
		1	<u> </u>	I

-	1	((US-5449941-\$ or US-5455432-\$ or	USPAT;	2002/05/14 08:34
		US-5039354-\$ or US-5056897-\$ or	US-PGPUB;	
		US-5159424-\$ or US-5260560-\$ or	EPO; JPO;	
		US-5369040-\$ or US-5451798-\$ or	DERWENT;	
		US-5734181-\$ or US-6166319-\$ or	IBM_TDB	
		US-6383576-\$ or US-5801401-\$ or		
		US-5989958-\$ or US-6344663-\$ or US-4113515-\$ or US-4473836-\$ or		
		US-5698869-\$ or US-5858811-\$ or		
		US-5976926-\$ or US-6031263-\$ or		
		US-6084248-\$ or US-6093937-\$ or		
		US-6099574-\$ or US-6130147-\$ or		
		US-6144581-\$ or US-6163066-\$).did. or		·
		(US-6166401-\$ or US-5465249-\$ or		
		US-4451391-\$ or US-6309907-\$ or		
		US-5061976-\$ or US-5625217-\$ or		1
		US-5661312-\$ or US-5798548-\$ or		
		US-6011279-\$ or US-6049110-\$ or		
		US-6249020-\$ or US-6306691-\$ or		1
	1	US-6313482-\$ or US-6365919-\$ or		İ
		US-5719410-\$ or US-5886368-\$ or		
1	1	US-4826778-\$ or US-6351411-\$ or		
	ļ	US-5557114-\$ or US-5562769-\$ or		
		US-5580380-\$ or US-5604357-\$ or		
	-	US-5623442-\$ or US-5629222-\$ or		
		US-5654208-\$ or US-5670790-\$ or		
		US-5714766-\$).did. or (US-5740104-\$ or		
		US-5754477-\$ or US-5786250-\$ or		
		US-5789276-\$ or US-5846859-\$ or		
		US-5877041-\$ or US-5886379-\$ or		
		US-5907775-\$ or US-6018166-\$ or		ļ.
		US-6034001-\$ or US-6075259-\$ or		ĺ
		US-5557122-\$ or US-5866930-\$ or		
1		US-5898197-\$ or US-5808336-\$ or		İ
		US-5393999-\$ or US-5539217-\$ or		
		US-4460670-\$ or US-4462150-\$ or		
		US-4507673-\$ or US-4657699-\$ or		
		US-4738729-\$ or US-4768072-\$ or		
		US-4769686-\$ or US-4841349-\$ or		
	ĺ '	US-4849797-\$ or US-4893273-\$).did. or		
		(US-5049950-\$ or US-5111430-\$ or		
		US-5145741-\$ or US-5235195-\$ or	İ	
		US-5260593-\$ or US-5293560-\$ or		
		US-5298796-\$ or US-5371383-\$ or		
		US-5407845-\$ or US-5415126-\$ or		
		US-5508543-\$ or US-5530581-\$ or		
		US-5477485-\$).did. or (US-20010032997-\$ or		
	1	US-20010049183-\$ or US-20020024050-\$ or		
		US-20020017647-\$).did. or (EP-291951-\$ or		
		EP-681333-\$).did. or (JP-62122275-\$ or	1	
		JP-63181473-\$ or JP-01115162-\$ or		
	!	JP-63219172-\$ or JP-04056769-\$ or		
		JP-63289960-\$ or JP-57126175-\$ or		
		JP-04061170-\$ or JP-56056677-\$ or		
		JP-02203564-\$).did. or (JP-04056769-\$ or		
		JP-62122275-\$ or JP-01115162-\$ or		
		EP-291951-\$ or EP-276002-\$ or		
		JP-07115191-\$).did.) and ohba.in.		
-	799	(257/77).CCLS.	USPAT;	2002/05/14 08:53
		·	US-PGPUB;	
]			EPO; JPO;	
<u> </u>			DERWENT;	
]			IBM TDB	
-	2	("5989958").PN.	USPAT;	2002/05/14 10:54
	_		US-PGPUB;	
			EPO; JPO;	
]	ļ		DERWENT;	
			IBM TDB	
<u> </u>				L

-	469	(257/314).CCLS.	USPAT;	2002/05/14 09:08
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	467	((257/314).CCLS.) not ((257/77).CCLS.)	USPĀT;	2002/05/14 09:24
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		0.50 /04.5	IBM_TDB	0000/05/14 00 04
_	1816	257/315	USPAT;	2002/05/14 09:24
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1577	(257/315 not (((257/314).CCLS.) not	USPAT;	2002/05/14 09:26
1		((257/77).CCLS.))) not ((257/77).CCLS.)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1375	(257/316).CCLS.	USPAT;	2002/05/14 10:54
			US-PGPUB; EPO; JPO;	
			DERWENT;	
	i		IBM TDB	
_	858	((((257/316).CCLS.) not 257/315) not	USPAT;	2002/05/14 10:55
		(((257/314).CCLS.) not ((257/77).CCLS.)))	US-PGPUB;	
		not ((257/77).CCLS.)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/05/44 40 45
-	0	("jp-3222367\$-\$.did.").PN.	USPAT;	2002/05/14 12:45
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	jp-03222367\$-\$.did.	USPAT;	2002/05/14 12:46
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	13	 in_0224431\$_\$ did	IBM_TDB USPAT;	2002/05/14 12:46
-	13	jp-0224431\$-\$.did.	USPAT; US-PGPUB;	2002/03/14 12:46
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2	jp-06224431\$-\$.did.	USPĀT;	2002/05/14 12:47
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	10	 jp-302828\$-\$.did.	IBM_TDB USPAT;	2002/05/14 12:48
)p 3020204 4.414.	US-PGPUB;	2002/00/14 12.40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	jp-06302828\$-\$.did.	USPAT;	2002/05/14 12:48
			US-PGPUB;	
	1		EPO; JPO; DERWENT;	
			IBM TDB	
l -	2	jp-07226507\$-\$.did.	USPAT;	2002/05/14 12:49
	_		US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
1		000FF070¢ ¢ 3''	IBM_TDB	0000/05/14 10 50
-	2	jp-08255878\$-\$.did.	USPAT;	2002/05/14 12:50
]			US-PGPUB; EPO; JPO;	
ļ			DERWENT;	
			IBM TDB	
	<u> </u>		_	

_	0	jp-08255878TR\$-\$.did.	USPAT;	2002/05/14 12:50
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	0	jp-08255878-TR\$-\$.did.	USPAT:	2002/05/14 12:50
		JP COZOCO SEL TOMBO	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/05/14 10 50
-	2	jp-60184681\$-\$.did.	USPAT;	2002/05/14 12:52
			US-PGPUB; EPO; JPO;	
}			DERWENT;	
			IBM TDB	
-	2	jp-60242678\$-\$.did.	USPAT;	2002/05/14 12:52
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1_	,	method adj2 using.clm. and optical adj	IBM_TDB USPAT;	2002/05/14 13:29
-	4	switch.ti.	US-PGPUB;	2002/03/14 13:29
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	714	(257/295).CCLS.	USPAT;	2002/05/15 13:13
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	0	("mram.ti,ab.").PN.	USPAT;	2002/05/15 13:13
		(,	US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
	07.6		IBM_TDB	0000 (05 (15 10 01
-	2/6	mram.ti,ab.	USPAT; US-PGPUB;	2002/05/15 13:21
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	988	((257/295).CCLS.) or mram.ti,ab.	USPĀT;	2002/05/15 13:21
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	873	 magnetic adj memory adj device	IBM_TDB USPAT;	2002/05/15 13:32
	","	magnitude and memory and device	US-PGPUB;	2002,00,10 10.02
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/05/15
-	4	((((257/295).CCLS.) or mram.ti,ab. or	USPAT;	2002/05/15 13:38
		(magnetic adj memory adj device)) and (ferrimagnetic or ferrimagnet) adj (layer	US-PGPUB; EPO; JPO;	
		or film)	DERWENT;	
			IBM TDB	
_	8	(((257/295).CCLS.) or mram.ti,ab. or	USPAT;	2002/05/15 14:56
		(magnetic adj memory adj device)) and	US-PGPUB;	
		(ferrimagnetic or ferrimagnet) adj2 (layer	EPO; JPO;	
		or film)	DERWENT;	
_	1	(((257/295).CCLS.) or mram.ti,ab. or	<pre>IBM_TDB USPAT;</pre>	2002/05/15 15:06
		(((257/293).CCLS.) or mram.tl,ab. or (magnetic adj memory adj device)) and	USPAT; US-PGPUB;	2002/03/13 13:06
		(ferrimagnetic or ferrimagnet) adj2 (layer	EPO; JPO;	
		or film) same orient\$5	DERWENT;	
			IBM_TDB	
-	1846	((257/295).CCLS.) or mram.ti,ab. or	USPAT;	2002/05/15 17:14
	}	(magnetic adj memory adj device)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
L	L	I	מעוב בוענג ן	

_	2	(((257/295).CCLS.) or mram.ti,ab. or	USPAT;	2002/05/15 15:51
		(magnetic adj memory adj device)) and data	US-PGPUB;	
		adj (layer or film) near15 (magnetization or magnetisation or magnetized or	EPO; JPO; DERWENT;	
		magnetised) near15 (turn or turning or	IBM TDB	
		orientation or orient or oriented)		
_	1	(((257/295).CCLS.) or mram.ti,ab. or	USPAT;	2002/05/15 15:59
		(magnetic adj memory adj device)) and data	US-PGPUB;	
		adj (layer or film) near15 (magnetization or magnetisation or magnetized or	EPO; JPO; DERWENT;	
		magnetised) near15 (turn or turning or	IBM TDB	
		orientation or orient or oriented) and	15.1_155	
		coercivity		
-	0	(((257/295).CCLS.) or mram.ti,ab. or	USPAT;	2002/05/15 17:01
		(magnetic adj memory adj device)) and data	US-PGPUB;	
		adj (layer or film) near15 (magnetization or magnetisation or magnetized or	EPO; JPO; DERWENT;	
		magnetised) near15 (turn or turning or	IBM TDB	
		orientation or orient or oriented) and		
	Į	coercivity and ferrimagnetic		
_	719	((257/295).CCLS.) or (magnetic adj memory	USPAT;	2002/05/15 17:17
		adj device) and af adj layer	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	44	(365/172).CCLS.	USPĀT;	2002/05/15 17:35
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	283	(365/173).CCLS.	USPAT;	2002/05/15 17:35
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	804	((365/171) or (365/172) or	USPAT;	2002/05/15 18:02
	}	(365/173)).CCLS.	US-PGPUB;	2002, 00, 20 20102
	İ		EPO; JPO;	
	:		DERWENT;	
_	0	(((365/171) or (365/172) or	IBM_TDB USPAT;	2002/05/15 18:08
		((365/173)).CCLS.) and (antiferrimagnetic	US-PGPUB;	2002/03/13 10.00
		or af) adj (layer of film) and (magnetic	EPO; JPO;	
		adj memory) and coercivity and (data adj	DERWENT;	
		storage near3 (layer or film))	IBM_TDB	0000/05/15 10-10
_	4	(((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic	USPAT; US-PGPUB	2002/05/15 18:10
		or af) adj (layer of film) and (magnetic	33 13135	
		adj memory) and coercivity		
_	4	(((365/171) or (365/172) or	USPAT;	2002/05/15 19:32
		(365/173)).CCLS.) and (antiferrimagnetic or af) adj (layer of film) and (magnetic	US-PGPUB	
		adj memory) and coercivity and (angle or		
		orient or orientation or oriented or turn		
		or turned or turning or rotate or rotated		
1_	0	or rotation)	IISDAT.	2002/05/15 18:31
-		(((365/171) or (365/172) or (365/173)).CCLS.) and ((synthetic adj	USPAT; US-PGPUB	2002/03/13 18:31
		ferrimagnetic or sf or artificial adj		
	1	ferrimagnetic) near6 (layer or film))		
-	0	(((365/171) or (365/172) or	USPAT;	2002/05/15 18:31
		(365/173)).CCLS.) and (synthetic adj ferrimagnetic or sf or artificial adj	US-PGPUB	
		ferrimagnetic or si or artificial adj ferrimagnetic)		
-	23	(synthetic adj ferrimagnetic or sf or	USPAT;	2002/05/15 18:36
1		artificial adj ferrimagnetic) and (mram or	US-PGPUB	
_	_	magnetic adj memory)	Henrm.	2002/05/15 10:20
-	2	(synthetic adj (ferrimagnet or ferrimagnetic) or sf or artificial adj	USPAT; US-PGPUB	2002/05/15 18:38
		ferrimagnetic) and (mram or magnetic adj	05 10105	
		memory).ti,ab.		
		·	·	

-	4	(((365/171) or (365/172) or	USPAT;	2002/05/15 19:44
		(365/173)).CCLS.) and (antiferrimagnetic	US-PGPUB	
		or femn or af) adj (layer of film) and		
		(magnetic adj memory) and coercivity and		
	ļ	(angle or orient or orientation or		
	1	oriented or turn or turned or turning or		
	1	rotate or rotated or rotation)		
-	4	(antiferrimagnetic or femn or af) adj	USPAT;	2002/05/15 19:46
	1	(layer of film) and (magnetic adj memory)	US-PGPUB	
	İ	and coercivity and (angle or orient or		
		orientation or oriented or turn or turned		
		or turning or rotate or rotated or		
1		rotation)		
_	4	(antiferrimagnetic or femn or af) adj	USPAT;	2002/05/15 19:48
	1	(layer of film) and (magnetic adj memory)	US-PGPUB;	
		and coercivity and (angle or orient or	EPO; JPO;	
		orientation or oriented or turn or turned	DERWENT;	
		or turning or rotate or rotated or	IBM TDB	
		rotation)	1511_155	
l _	4	1	USPAT;	2002/05/15 19:48
	1	(layer of film) and (magnetic adj memory)	US-PGPUB;	2002/03/13 13.40
	1	and coercivity	EPO; JPO;	
		and coefficient	DERWENT;	
			IBM TDB	
_	17	(antifornimagnotic or form or of) and	USPAT;	2002/05/15 19:51
I -	1	1 '	The state of the s	2002/03/13 19:31
	1	(magnetic adj memory) and coercivity	US-PGPUB; EPO; JPO;	
	İ		DERWENT;	
	0004	/	IBM_TDB	2002/05/15 10 52
-	8934	1 1	USPAT;	2002/05/15 19:52
		mtj or hard-soft adj mtj)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/05/15 01 15
-	1	1 ,	USPAT;	2002/05/15 21:17
		adj mtj or hard-soft adj mtj)	US-PGPUB;	İ
			EPO; JPO;]
			DERWENT;	
	_	#50 5504 OH	IBM_TDB	
-	1	"5966012".PN.	USPAT	2002/05/15 20:52
	1	"5841692".PN.	USPAT	2002/05/15 20:55
] -	1	"5801984".PN.	USPAT	2002/05/15 20:56
-	1	"5055158".PN.	USPAT	2002/05/15 20:57
-	1	"5055158".PN.	USPAT	2002/05/15 20:58
-	1	(antiferromagnetic or femn or af) and (hs	USPAT;	2002/05/15 21:24
1	1	adj mtj or hard-soft adj mtj)	US-PGPUB;	
1			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	2	("5605958").PN.	USPAT;	2002/05/15 21:24
1			US-PGPUB;	1
1			EPO; JPO;	
1			DERWENT;	
1			IBM_TDB	
-	3	("5650958").PN.	USPAT;	2002/05/15 22:05
1			US-PGPUB;	
			EPO; JPO;	
[DERWENT;	
İ	İ		IBM_TDB	
-	77	magnetic adj memory and spacer adj layer	USPAT;	2002/05/15 22:29
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	magnetic adj memory and (spacer adj layer	USPAT;	2002/05/15 22:30
i	1	near12 sf)	US-PGPUB;	
			EPO; JPO;	!
			DERWENT;	
			IBM TDB	
	•			·

_	77	magnetic adj memory and spacer adj layer	USPAT; US-PGPUB; EPO; JPO;	2002/05/15 22:48
			DERWENT; IBM_TDB	
_	7	magnetic adj memory and (spacer adj layer near5 antiferromagnetic)	USPAT; US-PGPUB;	2002/05/16 07:45
			EPO; JPO; DERWENT; IBM TDB	
_	3	magnetic adj memory and (spacer adj layer near5 antiferromagnetic) and (spacer	USPAT; US-PGPUB;	2002/05/16 08:01
		near12 different)	EPO; JPO; DERWENT;	
_	0	(spacer near12 antiferromagnetic near12	IBM_TDB USPAT;	2002/05/16 08:02
		different) and magnetic adj2 memory	US-PGPUB; EPO; JPO;	
	-	10 10	DERWENT; IBM_TDB	2002/05/16 00 45
_	5	spacer near12 antiferromagnetic near12 different	USPĀT; US-PGPUB; EPO; JPO;	2002/05/16 08:45
			DERWENT; IBM TDB	
_	295	(365/158).CCLS.	USPAT; US-PGPUB;	2002/05/16 08:45
			EPO; JPO; DERWENT;	
_	602	(365/171).CCLS.	IBM_TDB USPAT;	2002/05/16 08:46
			US-PGPUB; EPO; JPO;	
			DERWENT; IBM_TDB	
-	44	(365/172).CCLS.	USPAT; US-PGPUB;	2002/05/16 08:46
			EPO; JPO; DERWENT; IBM TDB	
_	283	(365/173).CCLS.	USPAT; US-PGPUB;	2002/05/16 08:46
			EPO; JPO; DERWENT;	
_	3429	(365/174).CCLS.	IBM TDB USPAT;	2002/05/16 08:46
			US-PGPUB; EPO; JPO;	
		V055 (00) - 225 5	DERWENT; IBM_TDB	
-	431	(257/30).CCLS.	USPAT; US-PGPUB;	2002/05/16 08:47
			EPO; JPO; DERWENT; IBM TDB	
_	4807	((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172).CCLS.) or ((365/173).CCLS.) or	USPAT; US-PGPUB;	2002/05/16 08:47
		((365/174).CCLS.) or ((257/30).CCLS.)	EPO; JPO; DERWENT;	
_	179	spacer and coercivity and	IBM_TDB USPAT;	2002/05/16 08:48
		antiferromagnetic	US-PGPUB; EPO; JPO;	
	4.4	///205/150\ 0010\ \ am //205/171\ 0010\ \	DERWENT; IBM_TDB	2002/05/16 12:56
_	11	(((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172).CCLS.) or ((365/173).CCLS.) or ((365/174).CCLS.) or ((365/174).CCLS.)	USPAT; US-PGPUB; EPO; JPO;	2002/05/16 13:56
		(spacer and coercivity and antiferromagnetic)	DERWENT; IBM TDB	
l		and the state of t		·

-	5	((((365/158).CCLS.) or ((365/171).CCLS.)	USPAT;	2002/05/16 14:30
		or ((365/172).CCLS.) or ((365/173).CCLS.)	US-PGPUB;	
		or ((365/174).CCLS.) or ((257/30).CCLS.))	EPO; JPO;	
		and (spacer and coercivity and	DERWENT;	
	_	antiferromagnetic)) and @pd<20000104	IBM_TDB	
-	0	mtj adj mr and world adj line and bottom	USPAT;	2002/05/16 14:31
		adj electrode	US-PGPUB;	
			EPO; JPO;	
		,	DERWENT;	
	_		IBM_TDB	
-	0	mtj adj mr and world adj line	USPAT;	2002/05/16 14:32
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1 1	med add my and stand add line	IBM_TDB	2002/05/16 14:22
-	1	mtj adj mr and word adj line	USPAT;	2002/05/16 14:33
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1_	7	"6114719"	IBM_TDB USPAT;	2002/05/16 15:30
_	/	0114/13	US-PGPUB;	2002/03/10 13:30
	į		EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
_	3	mtj and (current near12 (magnetization or	USPAT;	2002/05/16 16:37
		magnetized)) near12 (perpendicular or	US-PGPUB;	2002/03/10 10.3/
		orthogonal)	EPO; JPO;	
1	1	Of thogonary	DERWENT;	
			IBM TDB	
_	0	"not pinned" and (mram or mtj)	USPAT;	2002/05/16 16:44
	Ĭ	i not printed and (mram or me),	US-PGPUB;	2002/03/10 10:44
			EPO; JPO;	ļ
			DERWENT;	
			IBM TDB	
_	0	"not pinned" and (mram or mtj or	USPAT;	2002/05/16 16:45
		magneto-resistive or af adj layer)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	178	(hard same soft) and (mram or mtj or	USPAT;	2002/05/16 16:47
		magneto-resistive or af adj layer)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(soft-soft) and (mram or mtj or	USPĀT;	2002/05/16 16:47
		magneto-resistive or af adj layer)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/05/16 15 15
-	0	soft-soft and (mtj or mram or	USPAT;	2002/05/16 16:49
		magneto-resistive)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1_	11	 soft-soft	IBM_TDB USPAT;	2002/05/16 16:50
-		SOLU-SOLU	· ·	2002/05/16 16:50
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	soft-soft and magnetic	USPAT;	2002/05/16 16:50
			US-PGPUB;	======
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	3	mtj and second adj free	USPAT;	2002/05/16 20:54
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

-	17		USPAT;	2002/05/16 22:40
		(af adj layer reference adj layer or data	US-PGPUB;	
		adj layer or sens\$3 adj layer or pinned	EPO; JPO; DERWENT;	
		adj2 layer)	IBM TDB	
l _	3	(("5640343") or ("6269018") or	USPAT	2002/05/16 23:13
-]	("5966012")).PN.	USFAI	2002/03/10 23:13
l _	2		USPAT;	2002/11/04 11:23
		703432.ap.	US-PGPUB;	2002/11/04 11:25
			EPO; JPO;	
		•	DERWENT;	
	1		IBM TDB	
_	2	("5989958").PN.	USPAT;	2002/11/04 12:57
	_	(333333	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
	1		IBM TDB	
_	0	jp-03571261\$-\$.did.	USPAT;	2002/11/04 12:58
			US-PGPUB;	
			EPO; JPO;	
		*	DERWENT;	
	}		IBM_TDB	
-	8	,	JPO_	2002/11/04 13:00
		semiconductor		
-	2	"3571261"	USPAT;	2002/11/04 12:59
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	"carbide/amorophous".ti.	USPAT;	2002/11/04 15:49
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/11/01/01
-	0	·F · · · · · · · · · · · · · · · · · ·	USPAT;	2002/11/04 18:04
		adj affinity	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	329	optoelectric adj conversion	USPAT;	2002/11/04 18:04
	323	optoelectic day conversion	US-PGPUB;	2002/11/04 10:04
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2724	electron adj affinity	USPAT;	2002/11/04 18:04
	1		US-PGPUB;	,
			EPO; JPO;	
			DERWENT;	l
			IBM_TDB	
-	0	-1	USPAT;	2002/11/04 18:05
		affinity	US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
1] , , , , , , , , , , , , , , , , , , ,	IBM_TDB	0000/11/01/11
-	32	1 11 11 11 11 11 11 11 11	USPAT;	2002/11/04 18:06
		efficiency	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
l _		enteelectric adi conversion manual	IBM_TDB	2002/11/04 10:07
l ⁻	4	1 -1	USPAT;	2002/11/04 18:07
1		efficiency and silicon adj carbide	US-PGPUB;	
1	1		EPO; JPO; DERWENT;	
ł			IBM TDB	
_	3404	((257/77) or (257/314) or (257/315) or	USPAT;	2002/11/05 11:44
	5404	((257/77) of (257/314) of (257/315) of (257/316)).CCLS.	US-PGPUB;	2002,11,00 11.44
		(10.,010,,.0000.	EPO; JPO;	
			DERWENT;	
			IBM TDB	
L	·			

_	14	(((257/77) or (257/314) or (257/315) or	USPAT;	2002/11/05 11:46
		(257/316)).CCLS.) and breakdown adj	US-PGPUB;	
		voltage near15 silicon adj carbide	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	(((257/77) or (257/314) or (257/315) or	USPAT;	2002/11/05 11:47
		(257/316)).CCLS.) and electron adj	US-PGPUB;	
		affinity near15 silicon adj carbide	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	("6104054").PN.	USPAT;	2002/11/05 14:24
			US-PGPUB;	
			EPO; JPO;	Į.
			DERWENT;	
			IBM TDB	
_	8	(("5661312") or ("5798548") or ("5989958")	USPĀT	2003/01/27 10:34
		or ("5808336") or ("5369040") or		
		("5557122") or ("5393999") or		
	-	("5734181")).PN.		
_	0	jp-357126175\$-\$.did.	USPAT;	2003/01/27 10:38
		Jp coversus, trans	US-PGPUB;	=====================================
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	jp-57126175\$-\$.did.	USPAT;	2003/01/27 10:40
	_	jp ovizorio+ + tazat	US-PGPUB;	=====================================
	1		EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	jp-02203564\$-\$.did.	USPAT;	2003/01/27 10:40
		JP	US-PGPUB;	=====================================
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	13	(US-6084248-\$ or US-6031263-\$ or	USPAT	2003/03/21 13:50
		US-5976926-\$ or US-5858811-\$ or	001111	2003,03,21 13.30
		US-5698869-\$ or US-4473836-\$ or		
		US-4113515-\$ or US-6130147-\$ or		
		US-6144581-\$ or US-6099574-\$ or		İ
		US-6093937-\$ or US-6166401-\$ or		
		US-6163066-\$).did.		
_	57		USPAT: JPO	2003/03/21 13:51
_	1 0		JPO	2003/03/21 13:51
		optoelectronic	525	2000,00,21 10.01
_	1		JPO	2003/03/21 13:52
		heterojunction	0.0	2003,03,21 13.32
_	31	hamakawa.in. and conversion	JPO	2003/03/21 13:52
	, 51	,		

		1 5440041 A TO COORER A	Lugnie	T 0000 /00 /05
-	141	(US-5449941-\$ or US-6383576-\$ or	USPAT;	2003/03/25 11:00
		US-6166319-\$ or US-5451798-\$ or US-5734181-\$ or US-5260560-\$ or	US-PGPUB; EPO; JPO;	
		US-5886379-\$ or US-5786250-\$ or	DERWENT	
		US-5877041-\$ or US-5846859-\$ or	DEKWENT	
		US-5789276-\$ or US-5754477-\$ or	1	
		US-5740104-\$ or US-5670790-\$ or		
		US-5714766-\$ or US-5654208-\$ or		
		US-5623442-\$ or US-5580380-\$ or		
		US-5604357-\$ or US-5562769-\$ or		
		US-5557114-\$ or US-5530581-\$ or		
		US-5477485-\$ or US-5455432-\$ or		
		US-5407845-\$ or US-5415126-\$).did. or		
		(US-5298796-\$ or US-5293560-\$ or		
		US-5260593-\$ or US-5235195-\$ or		
		US-5145741-\$ or US-5111430-\$ or		
		US-5049950-\$ or US-4893273-\$ or		
		US-4841349-\$ or US-4769686-\$ or		
		US-4738729-\$ or US-4657699-\$ or		
		US-4462150-\$ or US-4460670-\$ or		
		US-6002143-\$ or US-5852306-\$ or US-4849797-\$ or US-5369040-\$ or		
		US-5039354-\$ or US-5159424-\$ or		
		US-5056897-\$ or US-4826778-\$ or		
		US-5886368-\$ or US-5719410-\$ or		
		US-5371383-\$ or US-6236590-\$ or		
		US-6166948-\$).did. or (US-5793697-\$ or		
		US-5640343-\$ or US-6205052-\$ or		
ļ		US-6178112-\$ or US-6197439-\$ or		
		US-6108177-\$ or US-5408377-\$ or		
		US-6365919-\$ or US-6313482-\$ or		
		US-6306691-\$ or US-6249020-\$ or		
		US-6018166-\$ or US-6133587-\$ or		
		US-6121633-\$ or US-6075259-\$ or		
		US-6049110-\$ or US-6011279-\$ or		
		US-5798548-\$ or US-5661312-\$ or		
		US-5539217-\$ or US-5465249-\$ or		
		US-5323040-\$ or US-4507673-\$ or		
		US-5625217-\$ or US-5061976-\$ or		
		US-6344663-\$ or US-6180958-\$).did. or (US-5989958-\$ or US-5801401-\$ or		
		US-5393999-\$ or US-5629222-\$ or		
		US-6309907-\$ or US-4768072-\$ or		
		US-4451391-\$ or US-6351411-\$ or		1
		US-5898197-\$ or US-5508543-\$ or		
		US-5808336-\$ or US-5866930-\$ or		
		US-5557122-\$ or US-6034001-\$ or		
		US-5907775-\$ or US-6166401-\$ or		
		US-6163066-\$ or US-6144581-\$ or		
		US-6093937-\$ or US-6099574-\$ or		
		US-6130147-\$ or US-6031263-\$ or		
		US-6084248-\$ or US-5976926-\$ or	1	
		US-5698869-\$ or US-4113515-\$ or		
]	-	US-4473836-\$).did. or (US-5858811-\$).did.		
		or (US-20020017647-\$ or US-20020036331-\$		
	ĺ	or US-20020041514-\$ or US-20020024050-\$ or		
		US-20010049183-\$ or US-20010032997-\$).did. or (EP-291951-\$ or US-5585986-\$ or		
		er (EP-291951-\$ or US-5585986-\$ or EP-681333-\$).did. or (JP-63219172-\$ or		
		JP-01115162-\$ or JP-06302828-\$ or		
		JP-07226507-\$ or JP-08255878-\$ or		
		JP-60184681-\$ or JP-60242678-\$ or		
		JP-63181473-\$ or JP-62122275-\$ or		
		JP-04056769-\$ or JP-03222367-\$ or		
		JP-02203564-\$ or JP-56056677-\$ or		
		JP-04061170-\$ or JP-57126175-\$ or		
		JP-06224431-\$ or JP-63289960-\$).did. or		
		(EP-276002-\$ or JP-07115191-\$ or		
		JP-62122275-\$ or JP-60184681-\$ or		
]		JP-01115162-\$ or JP-04056769-\$ or		
L		US-6081446-\$ or EP-291951-\$).did.		1

-	1	((US-5449941-\$ or US-6383576-\$ or	USPAT;	2003/03/25 11:00
		US-6166319-\$ or US-5451798-\$ or	US-PGPUB;	
		US-5734181-\$ or US-5260560-\$ or	EPO; JPO;	
		US-5886379-\$ or US-5786250-\$ or	DERWENT	
		US-5877041-\$ or US-5846859-\$ or		-
		US-5789276-\$ or US-5754477-\$ or		
		US-5740104-\$ or US-5670790-\$ or		
		US-5714766-\$ or US-5654208-\$ or		
		US-5623442-\$ or US-5580380-\$ or		
		US-5604357-\$ or US-5562769-\$ or		
		US-5557114-\$ or US-5530581-\$ or		
		US-5477485-\$ or US-5455432-\$ or		
		US-5407845-\$ or US-5415126-\$).did. or		
		(US-5298796-\$ or US-5293560-\$ or		
		US-5260593-\$ or US-5235195-\$ or		
		1		
		US-5145741-\$ or US-5111430-\$ or		
		US-5049950-\$ or US-4893273-\$ or		1
		US-4841349-\$ or US-4769686-\$ or		
		US-4738729-\$ or US-4657699-\$ or		
		US-4462150-\$ or US-4460670-\$ or		1
1	Ì	US-6002143-\$ or US-5852306-\$ or		1
		US-4849797-\$ or US-5369040-\$ or		
		US-5039354-\$ or US-5159424-\$ or		
		US-5056897-\$ or US-4826778-\$ or		
		US-5886368-\$ or US-5719410-\$ or		
		US-5371383-\$ or US-6236590-\$ or		
		US-6166948-\$).did. or (US-5793697-\$ or	1	
		US-5640343-\$ or US-6205052-\$ or	1	
		US-6178112-\$ or US-6197439-\$ or		
		US-6108177-\$ or US-5408377-\$ or	ì	
		US-6365919-\$ or US-6313482-\$ or		
		US-6306691-\$ or US-6249020-\$ or		
		US-6018166-\$ or US-6133587-\$ or		
		1		
		US-6121633-\$ or US-6075259-\$ or		
		US-6049110-\$ or US-6011279-\$ or		
		US-5798548-\$ or US-5661312-\$ or		
		US-5539217-\$ or US-5465249-\$ or		
		US-5323040-\$ or US-4507673-\$ or		
		US-5625217-\$ or US-5061976-\$ or	1	
		US-6344663-\$ or US-6180958-\$).did. or		
		(US-5989958-\$ or US-5801401-\$ or		
		US-5393999-\$ or US-5629222-\$ or		
		US-6309907-\$ or US-4768072-\$ or		
	i	US-4451391-\$ or US-6351411-\$ or		į
		US-5898197-\$ or US-5508543-\$ or		İ.
1 1		US-5808336-\$ or US-5866930-\$ or		
		US-5557122-\$ or US-6034001-\$ or		
		US-5907775-\$ or US-6166401-\$ or		
		US-6163066-\$ or US-6144581-\$ or	-	
		US-6093937-\$ or US-6099574-\$ or		. 1
		US-6130147-\$ or US-6031263-\$ or		
		US-6084248-\$ or US-5976926-\$ or		
		US-5698869-\$ or US-4113515-\$ or		
		US-4473836-\$).did. or (US-5858811-\$).did.		
		or (US-20020017647-\$ or US-20020036331-\$		<u> </u>
		or US-20020041514-\$ or US-20020024050-\$ or		
		US-20010049183-\$ or US-20010032997-\$).did.		
		or (EP-291951-\$ or US-5585986-\$ or	1	
		EP-681333-\$).did. or (JP-63219172-\$ or		
		JP-01115162-\$ or JP-06302828-\$ or		
		JP-07226507-\$ or JP-08255878-\$ or		
		JP-60184681-\$ or JP-60242678-\$ or		l i
		JP-63181473-\$ or JP-62122275-\$ or		
		JP-04056769-\$ or JP-03222367-\$ or	1	
		JP-02203564-\$ or JP-56056677-\$ or		
		JP-04061170-\$ or JP-57126175-\$ or		
		JP-06224431-\$ or JP-63289960-\$).did. or		
		(EP-276002-\$ or JP-07115191-\$ or		
		JP-62122275-\$ or JP-60184681-\$ or		
]		JP-01115162-\$ or JP-04056769-\$ or		
]		US-6081446-\$ or EP-291951-\$).did.) and		
		miyawaki.in.		
L		mryawakt.III.		L

-	1	("4460670").PN.	USPAT	2003/03/25 17:05
-	1	("4462150").PN.	USPAT	2003/03/25 17:05
-	10	(transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide	USPAT; US-PGPUB;	2003/08/18 17:38
		near12 (x or y))	EPO; JPO;	
		neariz (x or y))	DERWENT;	
			IBM TDB	
_	11	(transistor MOS MOSFET) and gate near12	USPAT;	2003/08/18 17:35
		("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x"	US-PGPUB;	
		"Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y"	EPO; JPO;	
		silicon adj carbide near12 (x or y))	DERWENT;	
			IBM_TDB	
-	1	((transistor MOS MOSFET) and gate near12	USPAT;	2003/08/18 17:35
		("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x"	US-PGPUB;	
		"Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y))) not	EPO; JPO; DERWENT;	
		((transistor MOS MOSFET) and gate near12	IBM TDB	
		("Si.sub.1-x C.sub.x" silicon adj carbide	I TOM_I DO	
		near12 (x or y)))		
_	8	gate near12 ("Si.sub.1-x C.sub.x" silicon	USPAT;	2003/08/18 17:40
		adj carbide near12 (x or y)) and	US-PGPUB;	
1		257/\$9.ccls.	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	0	(gate near12 ("Si.sub.1-x C.sub.x" silicon	USPAT;	2003/08/18 17:39
		adj carbide near12 (x or y)) and	US-PGPUB;	
		257/\$9.ccls.) not ((transistor MOS MOSFET)	EPO; JPO;	
		and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y"	DERWENT;	
		"Si.sub.y C.sub.1-y" silicon adj carbide	IBM_TDB	
		near12 (x or y)))		
_	10		USPAT;	2003/08/18 17:40
		adj carbide near12 (x or y))	US-PGPUB;	1
		1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	, , , , , , , , , , , , , , , , , , , 	USPAT;	2003/08/18 18:18
		adj carbide near12 (x or y))) not	US-PGPUB;	
		((transistor MOS MOSFET) and gate near12	EPO; JPO; DERWENT;	
		("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y"	IBM TDB	
		silicon adj carbide near12 (x or y)))	1511_155	
-	2	("5661312").PN.	USPAT;	2003/08/19 09:13
	_	, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/00/100
_	0	("jp-57125175\$-\$.did.").PN.	USPAT;	2003/08/19 09:14
			US-PGPUB;	
			EPO; JPO; DERWENT;	
	1		IBM TDB	
-	0	jp-57125175\$-\$.did.	USPAT;	2003/08/19 09:14
	1		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	2	jp-57126175\$-\$.did.	USPAT;	2003/08/19 10:49
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	229	 barrier near6 gate and silicon adj carbide	USPAT;	2003/08/19 09:35
	223	ballier heart gate and billeon adj carbide	US-PGPUB;	2000,00715 05.55
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5	1	USPĀT;	2003/08/19 10:02
		carbide	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
	L	<u> </u>	IBM_TDB	L

-	1	"5506421".PN.	USPAT	2003/08/19 09:37
-	1	"5495124".PN.	USPAT	2003/08/19 09:39
-	1	"5451797".PN.	USPAT	2003/08/19 09:39
-	1	"5396085".PN.	USPAT	2003/08/19 09:43
_	1	"5393999".PN.	USPAT	2003/08/19 09:45
_	15	gate near6 breakdown near6 (silicon adj	USPAT;	2003/08/19 10:12
		carbide "Si.sub.1-x" adj "C.sub.x"	US-PGPUB;	
		"Si.sub.x" adj "C.sub.1-x")	EPO; JPO;	
		barbabin adj broabia n	DERWENT;	
			IBM TDB	
	304	"Si.sub.1-x" adj "C.sub.x" "Si.sub.x" adj	USPAT;	2003/08/19 10:13
_	304	"C.sub.1-x"		2003/08/19 10:13
		"C.Sub.1-x"	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12	1 .	USPAT;	2003/08/19 10:14
	Í	"C.sub.1-x") and gate near6 breakdown	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
			IBM TDB	
_	2	("5369040").PN.	USPAT;	2003/08/19 10:58
	1		US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
			IBM TDB	
1_	0	("MOSadjphotodetector.ti,ab.").PN.	USPAT;	2003/08/19 10:58
_		Tobad Procede Court (1, ab. 1. FN.	US-PGPUB;	2003/00/19 10.36
			EPO; JPO;	
	1			
	1		DERWENT;	
			IBM_TDB	0000/65/15
-	8	MOS adj photodetector.ti,ab.	USPAT;	2003/08/19 11:50
			US-PGPUB;	
	[EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	17	gate near6 polysilicon near6 carbon	USPAT;	2003/08/19 12:12
]	J	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
l _	1	"4963953".PN.	USPAT	2003/08/19 12:03
1 _	1			
-	1	"4780394".PN.	USPAT	2003/08/19 12:04
-	1	"4352237".PN.	USPAT	2003/08/19 12:04
1	1	"4189826".PN.	USPAT	2003/08/19 12:04
-	4	("3497773" "3622382" "3728590"	USPAT	2003/08/19 12:07
		"3896485").PN.	1	
-	43	3896485.URPN.	USPAT	2003/08/19 12:07
-] 1		USPAT;	2003/08/19 12:13
	-	source and channel and drain	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	İ		IBM_TDB	
-	1	(MOS MOSFET) adj photodetector.ti,ab,clm.	USPĀT;	2003/08/19 12:16
		and source and channel and drain	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	395	photodotector tilah alm and source and	USPAT;	2003/08/19 12:17
-	3,93	photodetector.ti,ab,clm. and source and		2003/00/19 12:1/
		channel and drain	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	100	photodetector.ti,ab,clm. and source near20	USPAT;	2003/08/19 12:17
		channel near20 drain near20 gate	US-PGPUB;	
		_	EPO; JPO;	
			DERWENT;	
			IBM TDB	ļ
-	0	photodetector.ti,ab,clm. and source near20	USPAT;	2003/08/19 12:19
	ĺ	channel near20 drain near20 gate near20	US-PGPUB;	
		(sic silicon adj carbide)	EPO; JPO;	
1		(010 Difficult day carpide)	DERWENT;	
1		<u></u>	IBM_TDB	

-	1	photodetector.ti,ab,clm. and source near20	USPAT; US-PGPUB;	2003/08/19 12:23
		channel near20 drain near20 gate near20 polysilicon	EPO; JPO;	
		porystricon	DERWENT;	
			IBM TDB	
_	7	photodetector.ti,ab,clm. and source near20	USPAT;	2003/08/19 13:12
		channel near20 drain near20 gate near20	US-PGPUB;	
		(silicon polysilicon)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	("5808336").PN.	USPAT;	2003/08/19 13:13
	ļ		US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	51	floating adj gate and photodetector and	USPAT;	2003/08/19 13:55
	31	source and drain and channel	US-PGPUB;	2003,00,13 13.33
		boured and arain and onamer	EPO; JPO;	
	ļ		DERWENT;	
			IBM TDB	
_	65	double-poly near12 gate	USPAT;	2003/08/19 15:12
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		W4050050W 732	IBM_TDB	0000/00/00 00 00
-	0	"4963953".PN.	USPAT	2003/08/19 15:07
-	21	(("3792465") or ("4118795") or ("4384349")	USPAT	2003/08/19 15:29
		or ("4816883") or ("4897710") or ("5317535") or ("5366713") or ("5388069")		
		or ("5424993") or ("5438544") or		
		("5441901") or ("5467306") or ("5493140")		
		or ("5672889") or ("5828101") or		
		("5861346") or ("5912837") or ("5926740")		
		or ("6297521") or ("6307775") or		
		("6309907")).PN.		
-	9	((("3792465") or ("4118795") or	USPAT;	2003/08/19 16:01
		("4384349") or ("4816883") or ("4897710")	US-PGPUB;	
		or ("5317535") or ("5366713") or	EPO; JPO;	
		("5388069") or ("5424993") or ("5438544")	DERWENT;	
İ		or ("5441901") or ("5467306") or ("5493140") or ("5672889") or ("5828101")	IBM_TDB	
		or ("5861346") or ("5912837") or		
		("5926740") or ("6297521") or ("6307775")		
		or ("6309907")).PN.) and (silicon adj		
	1	carbide or carbon near3 (polysilicon		
		silicon))		
-	122	silicon adj carbide and monocrystalline	USPAT;	2003/08/19 16:02
		and power adj2 (MOS MOSFET device)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/00/10 15 55
-	59	silicon adj carbide near12 monocrystalline	USPAT;	2003/08/19 16:02
		and power adj2 (MOS MOSFET device)	US-PGPUB;	
			EPO; JPO; DERWENT;	[
			IBM TDB	
_	13	silicon adj carbide near12 monocrystalline	USPAT;	2003/08/19 16:04
	13	and power adj2 (MOS MOSFET	US-PGPUB;	-555,55,15 15.01
		device).ti,ab,clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1430	silicon adj carbide near6 (MOS MOSFET	USPĀT;	2003/08/19 16:05
		device).ti,ab,clm.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1	silion odi cambida sassa sassa (1900	IBM_TDB	2002/00/10 10:05
-	111	silicon adj carbide near6 power near6 (MOS	USPAT;	2003/08/19 16:05
		MOSFET device).ti,ab,clm.	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
L	L			LJ

-	55	silicon adj carbide near6 power near6 (MOS MOSFET).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO;	2003/08/19 16:05
İ			DERWENT;	
-	6	silicon adj carbide near6 power near6 (MOS MOSFET).ti,ab,clm. and monocrystalline near6 silicon adj carbide	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/08/19 16:15
		nears sizioon aaj sarbias	DERWENT;	
_	1811	amorphous adj silicon adj carbide	IBM_TDB USPAT; US-PGPUB;	2003/08/19 16:16
			EPO; JPO; DERWENT; IBM_TDB	
-	73	amorphous adj silicon adj carbide and grain adj size	USPAT; US-PGPUB; EPO; JPO;	2003/08/19 16:16
			DERWENT;	
-	2	amorphous adj silicon adj carbide near12 grain adj size	IBM_TDB USPAT; US-PGPUB;	2003/08/19 16:32
			EPO; JPO; DERWENT; IBM_TDB	
-	23	epitaxial\$2 near12 silicon adj carbide near12 method and (monocrystal monocrystalline)	USPĀT; US-PGPUB; EPO; JPO;	2003/08/19 16:34
			DERWENT; IBM_TDB	0000/00/10 15 05
-	5	epitaxial\$2 near12 silicon adj carbide near12 method near12 (monocrystal monocrystalline)	USPAT; US-PGPUB; EPO; JPO;	2003/08/19 16:35
			DERWENT; IBM TDB	
_	463	method near12 epitaxial\$2 near12 (monocrystal monocrystalline)	USPAT; US-PGPUB; EPO; JPO;	2003/08/19 16:38
			DERWENT;	
_	112	method near12 epitaxial\$2 near12 (monocrystal monocrystalline) and	IBM_TDB USPAT; US-PGPUB;	2003/08/19 16:59
		117/\$6.ccls.	EPO; JPO; DERWENT; IBM TDB	
-	112	method near12 epitaxial\$2 near12 crystallinity	USPĀT; US-PGPUB;	2003/08/19 16:59
			EPO; JPO; DERWENT; IBM TDB	
-	0	method near12 epitaxial\$2 near12 crystallinity and silicon adj carbide	USPĀT; US-PGPUB;	2003/08/19 17:00
			EPO; JPO; DERWENT;	
-	0	method near12 epitaxial\$2 near12 ensur\$3 near12 crystallinity	IBM_TDB USPAT; US-PGPUB;	2003/08/19 17:00
			EPO; JPO; DERWENT; IBM TDB	
-	49	monocrystalline near4 silicon adj carbide and power.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO;	2003/08/19 17:01
			DERWENT; IBM TDB	
_	2	monocrystalline near4 silicon adj carbide near6 breakdown and power.ti,ab,clm.	USPĀT; US-PGPUB;	2003/08/19 17:02
			EPO; JPO; DERWENT; IBM TDB	
		L		

_	2	("5,449,925").PN.	USPAT; US-PGPUB;	2003/08/19 17:02
			EPO; JPO;	
			DERWENT; IBM TDB	
-	2	("5449925").PN.	USPĀT;	2003/08/19 17:03
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	1	(("5449925").PN.) and epitaxial\$3	USPAT;	2003/08/19 17:05
			US-PGPUB; EPO; JPO;	
			DERWENT;	
	1.0		IBM_TDB	0000/00/10 17 00
-	10	epitaxial\$3 near6 grow\$3 near6 monocrystalline near6 silicon adj carbide	USPAT; US-PGPUB;	2003/08/19 17:08
		monocification near officer any careful	EPO; JPO;	
			DERWENT;	
_	14	grow\$3 near6 monocrystalline near6 silicon	IBM_TDB USPAT;	2003/08/19 17:08
		adj carbide.ti,ab,clm.	US-PGPUB;	2000,00,13 1,100
			EPO; JPO;	
			DERWENT; IBM TDB	
_	3		USPĀT;	2003/08/19 17:09
		near6 silicon adj carbide.ti,ab,clm.	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	1	1	USPAT;	2003/08/19 17:09
		near6 silicon adj carbide.ti,ab,clm. and power.ti,ab,clm.	US-PGPUB; EPO; JPO;	
		pono2, 02, 02, 02	DERWENT;	
	16	method near6 (growth growing) near6	IBM_TDB USPAT;	2003/08/19 17:11
-	10	(monocrystalline monocrystal) near12	US-PGPUB;	2003/06/19 17:11
		(silicon adj carbide sic)	EPO; JPO;	
			DERWENT; IBM TDB	
_	13	method near6 (growth growing) near6	USPAT;	2003/08/19 17:20
		(monocrystalline monocrystal) near12	US-PGPUB;	
		(silicon adj carbide sic) and epitaxial\$2	EPO; JPO; DERWENT;	
			IBM TDB	
-	2	jp-57126175\$-\$.did.	USPAT;	2003/08/19 17:25
			US-PGPUB; EPO; JPO;	İ
			DERWENT;	
_	13	epitaxy near6 (grain crystal) adj size	IBM_TDB USPAT;	2003/08/19 17:39
	13	epicany hearo (grain crystal) adj Size	US-PGPUB;	2003/00/19 17:39
			EPO; JPO;	
			DERWENT; IBM TDB	
_	4	(work adj function workfunction) near12	USPAT;	2003/08/19 17:41
		crystallinity	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	184995	(work adj function workfunction) near12	USPAT;	2003/08/19 17:41
		silicon carbide	US-PGPUB; EPO; JPO;	
			DERWENT;	
_	15	(work add function workfunction) nos-12	IBM_TDB USPAT;	2003/08/19 17:43
-	12	(work adj function workfunction) near12 silicon adj carbide	US-PGPUB;	2003/00/19 1/:43
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	15	(work adj function workfunction) near12	USPAT;	2003/08/19 17:58
		crystalline near6 amorphous	US-PGPUB;	
		•	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	("carbonadjgate").PN.	USPAT;	2003/08/19 17:59
			US-PGPUB;	j
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	9657	gate adj gate	USPAT;	2003/08/19 17:59
			US-PGPUB;	
l.			EPO; JPO;	
	!		DERWENT;	
			IBM TDB	
-	0	carbon adj gate and source and drain	USPAT;	2003/08/19 18:00
İ			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
Ì			IBM TDB	
_	23	carbon adj gate	USPAT;	2003/08/19 18:00
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	19	carbon adj gate and (257/\$9.ccls.	USPAT;	2003/08/19 18:03
		117/\$9.ccls. 438/\$9.ccls.)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	14	"carbon gate" and (257/\$9.ccls.	USPĀT;	2003/08/19 18:04
		117/\$9.ccls. 438/\$9.ccls.)	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	63		USPAT;	2003/08/20 10:00
		"si.sub.1-x" adj "c.sub.x") and (energy	US-PGPUB;	
		adj gap or band adj energy)	EPO; JPO;	
			DERWENT;	
			IBM TDB	ļ